

**Wafer data**  
**Star120**  
**(900V/120A)**  
**June 2026**

# Features

**GaNPower innovative all-GaN-IC enables 3.8V turn-on voltage and +/-20 V regulated gate driving.**

**Enhanced system reliability and compatibility with conventional gate drivers (\*).**

**Regulated gate driving enables anti-ringing protection / ESD protection**

**Lossless source side current sensing**

(\* ) May require adjustment and increase of isolated auxiliary power supply of driver board if driving several parallelized Star120.

# Content



**Basic wafer info/DC data**

**Dynamic test data**

**Chip probe data**

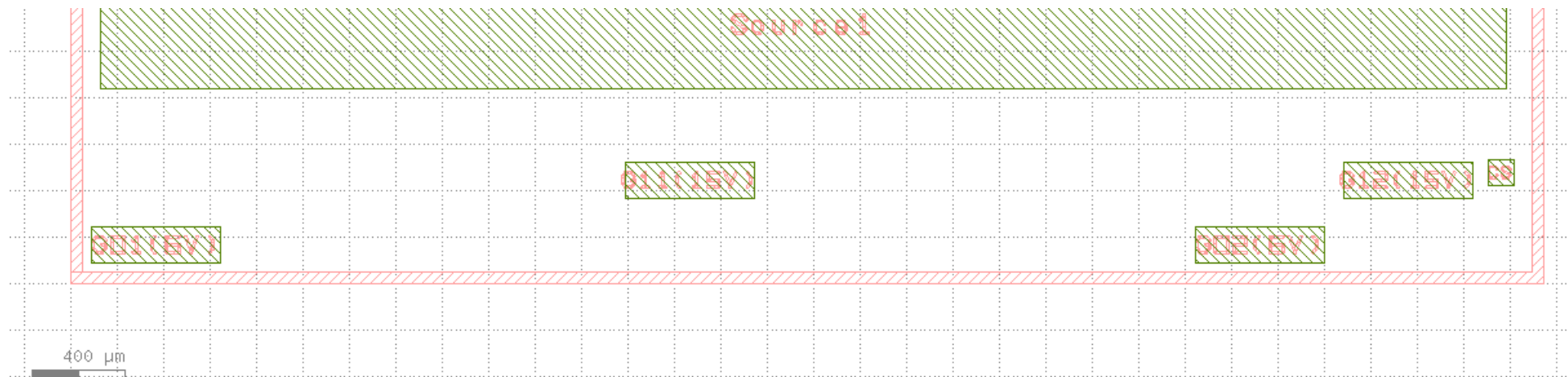
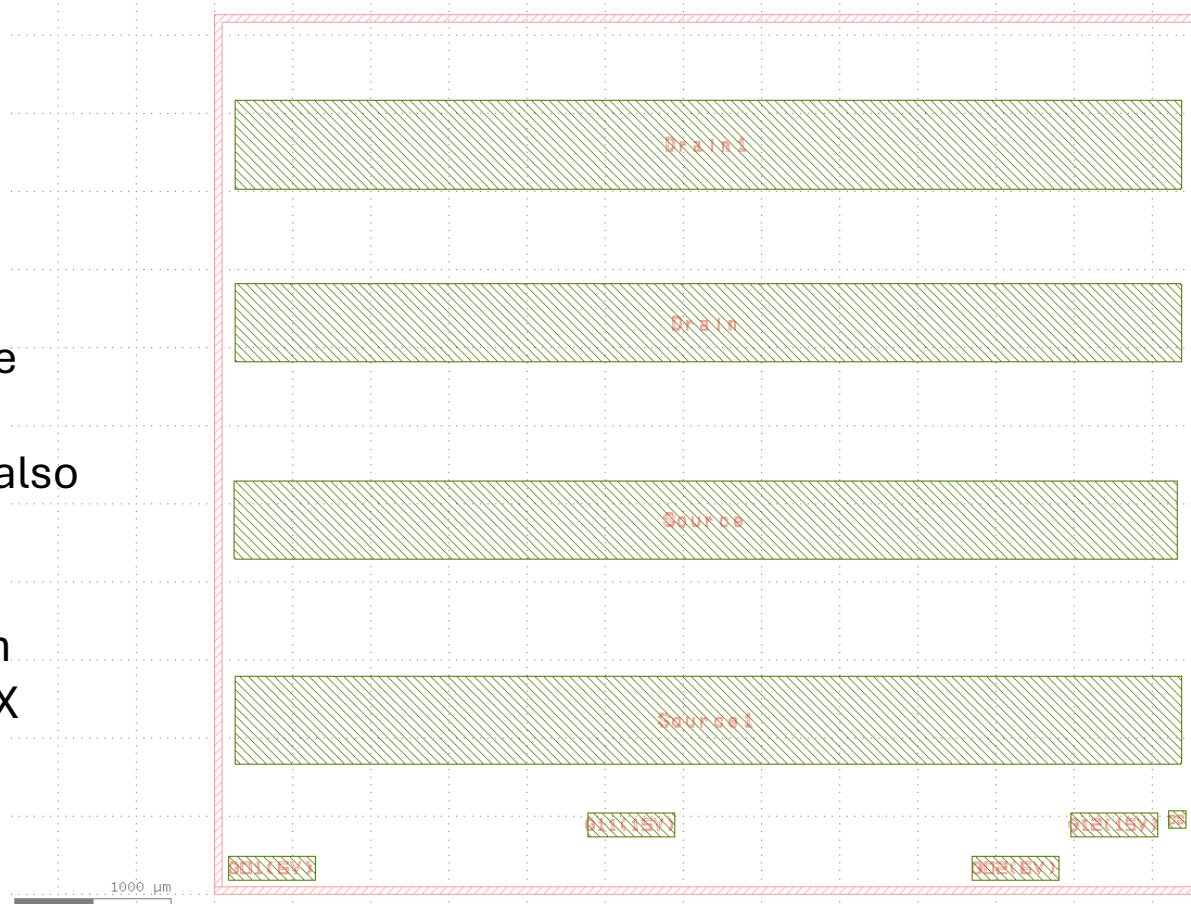
**App notes**

Device-name	x-size	y-size
Star120	6345.90	5634.28

Star120  
Version 1

Note that G11(15V) and G12(15V) are internally connected.  
Similarly, G01(6V) and G02(6V) are also internally connected.

For best gate control uniformity, both G1X (for 12/15V driving) or both G0X (for 6V driving) shall be used if wire bonding configuration allows.



**Main switch FET channel width: 1,426,822 um**

Star120  
Version 1

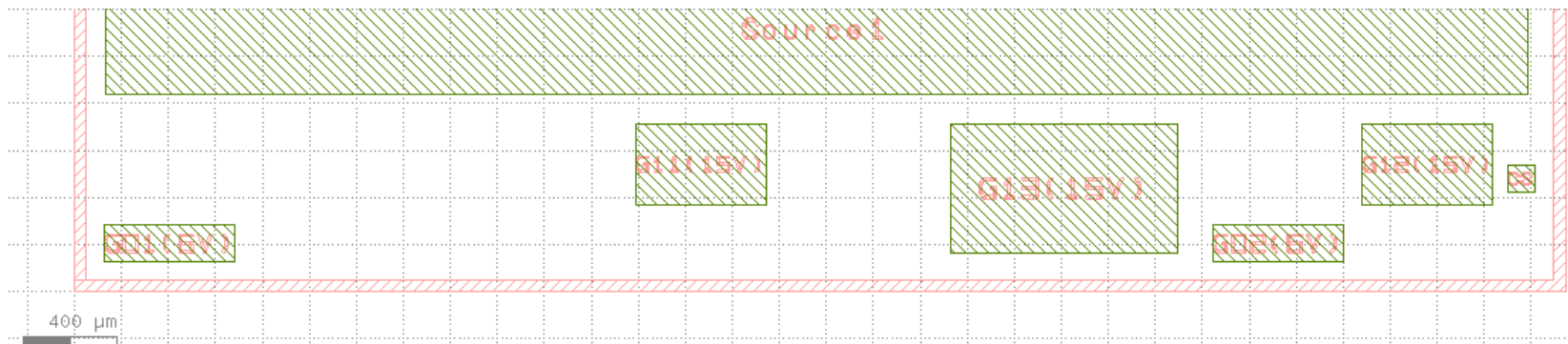
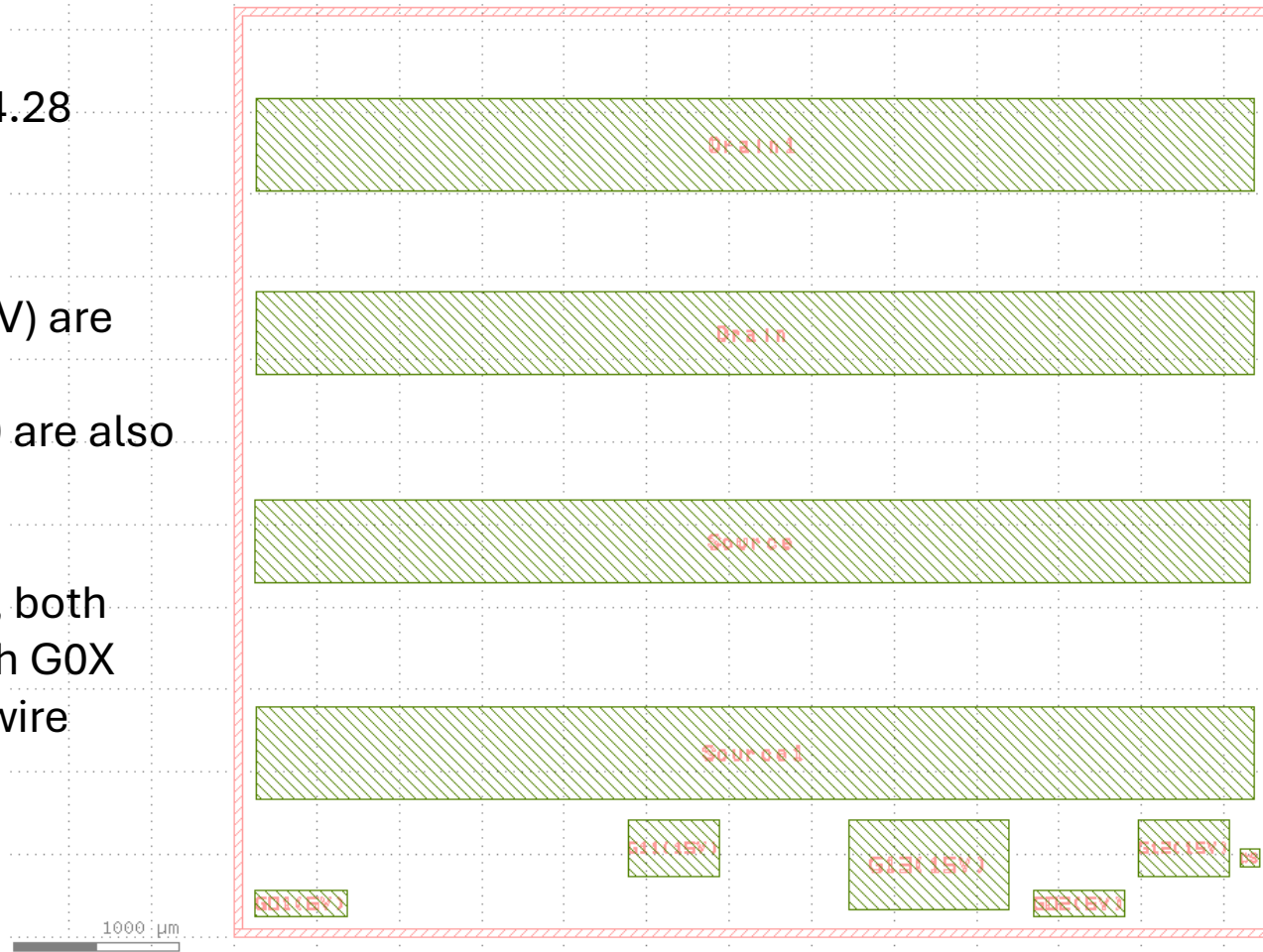
<b>PAD</b>	<b>Dx</b>	<b>Dy</b>	<b>Center_x</b>	<b>Center_y</b>
<b>G01(6V)</b>	<b>555.00</b>	<b>155.00</b>	<b>368.30</b>	<b>168.30</b>
<b>G11(15V)</b>	<b>585.00</b>	<b>185.00</b>	<b>2664.55</b>	<b>446.30</b>
<b>Source</b>	<b>6032.72</b>	<b>500.00</b>	<b>3144.16</b>	<b>2397.14</b>
<b>Source1</b>	<b>6053.72</b>	<b>560.00</b>	<b>3156.66</b>	<b>1116.70</b>
<b>Drain</b>	<b>6053.72</b>	<b>500.00</b>	<b>3156.66</b>	<b>3657.14</b>
<b>Drain1</b>	<b>6053.72</b>	<b>567.00</b>	<b>3156.66</b>	<b>4799.98</b>
<b>CS</b>	<b>111.00</b>	<b>111.00</b>	<b>6158.02</b>	<b>479.30</b>
<b>G02(6V)</b>	<b>555.00</b>	<b>155.00</b>	<b>5121.95</b>	<b>168.30</b>
<b>G12(15V)</b>	<b>585.00</b>	<b>185.00</b>	<b>5759.20</b>	<b>446.30</b>

Device-name	x-size	y-size
Star120	6345.90	5634.28

Note that G11(15V) and G12(15V) are internally connected.  
 Similarly, G01(6V) and G02(6V) are also internally connected.

For best gate control uniformity, both G1X (for 12/15V driving) or both G0X (for 6V driving) shall be used if wire bonding configuration allows.

Star120  
Version 2



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=====
PAD          Dx          Dy          Center_x    Center_y
-----
Drain        6053.29  500.00     3156.45     3657.14
Drain1       6053.29  567.00     3156.45     4799.98
Source       6032.14  500.00     3143.87     2397.14
Source1      6053.29  560.00     3156.45     1116.70
G11(15V)    555.00   345.00     2664.55     541.30
G12(15V)    555.00   345.00     5759.20     541.30
G13(15V)    970.00   548.00     4211.88     439.80
G01(6V)     555.00   155.00     404.30      204.30
G02(6V)     555.00   155.00     5121.95     204.30
CS           111.00   111.00     6157.44     479.30
=====

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Star120  
Version 2

# Basic specifications

Back metal	optional
Front metal	AlCu 4μm
Wafer diameter	6 inch
Wafer thickness before dicing	1000 μm
Recommended die thickness after dicing	150-250μm
Street width	80 μm
Recommended storage	N <sub>2</sub> environment

# Wire bonding suggestion

Larger pads use 10mil or 12mil Al .

Smaller pads use Cu, PdCu , or Au (1.5 mil – 2 mil)

Backside must be glued to backplate using conductive glue or be soldered after back metal

Backplate must be connected to the source of the GaNFET using wire bonding (low stress Al-wire recommended).

Pressurized Ag sintering should be avoided while pressureless Ag sintering is recommended for best thermal performance.

# Characteristics

		Condition	min	typical	max	
Ids-max	Max current at 125°C	Vgs=6V/15V (125°C)		120		A
Ids-max	Max current at 25°C	Vgs=6V/15V (25°C)		240		A
Vds-max	D-S breakdown voltage	Vgs=0V (25°C) < 10uA		900		V
Vg0s	Original gate voltage		-3		7	V
Vg1s	Regulated		-20		20	
Vgth (G0)	Gate threshold voltage	Vgs=Vds, Ids=35mA		1.3		V
Vg1th_lin (G1)	Regulated threshold	Vds=0.01V, Ids=100 mA	2.67	3.89	5.1	V
Vg1th_sat (G1)	Regulated threshold	Vds=0.01V, Ids=100 mA		2.35	4.02	V
Rdson	On resistance	Vg0s=6V/Vg1s=15V, Ids=1A (25°C)	9.4	13.3	20	mΩ
Rdson (150°C)	On resistance	Vg0s=6V/Vg1s=15V, Ids=1A (150°C)	26	38	59	mΩ
Vcs	Current sensing	Ids=+/-120A	-2.5		2.5	V
Qg	Gate charge	Vbus=500V , Turn-off from Ids=60A Vg0s from 6V to 0V (25°C)		29		nC

		Condition	min	typical	max	
Gm-Max	Max transconductance		357	640		mS
IDSS	Drain leakage	Vg1s=0V / Vg0s=0V, Vds=900V (25°C)		47	200	μA
IDSS(150°C)	Drain leakage	Vg1s=0V / Vg0s=0V, Vds=900V (150°C)		215	2345	μA
IDSS(150°C)	Drain leakage	Vg1s=0V / Vg0s=0V, Vds=900V (150°C)		374	2354	μA
IGSSF	Forward gate leakage	Vg1s=6V, Vds=0V (25°C)		184		μA
-IGSSR	Reverse gate leakage	Vg1s=-6V, Vds=0V (25°C)		106	817	μA
-IGSSR(150°C)	Reverse gate leakage	Vg1s=-6V, Vds=0V (150°C)		131	930	uA
Max_Isoff	Source leakage	Vg=Vs=Vb=GND, Vd=800V		0.6	7	μA
Isub	Bulk/substrate leakage	Vs=Vg=Vd=800V, B=GND		5.2		μA
Eoff	Turn-off energy	Vg=-2V/12V, Ids=60A		84.7		μJ
Tfall	Fall time			13.3		ns
Tdoff	Turn-off delay			35		ns
Eon	Turn-on energy			439		μJ
Trise	Rise time			39		ns
Tdon	Turn-on delay			12		ns

<b>DUT</b>	<b>Transient</b>	<b>Tdon/Tdoff (ns)</b>	<b>Trise/Tfall (ns)</b>	<b>Ton/Toff (ns)</b>	<b>Eloss (uJ)</b>	<b>Load</b>
<b>Star120-V1</b> <b>Vg=-1.3/12 V</b> <b>Rg = 2ohm</b>	Turn-off	39	20	59	254	400 V 92 A
	Turn-on	9	60	69	1062	
<b>Star120-V1</b> <b>Vg=-3.3/12 V</b> <b>Rg = 2ohm</b>	Turn-off	25	13	37	157	400 V 99 A
	Turn-on	11	98	109	1549	

$R_{GOFF} = 6.8\Omega$  for all

$V_{GS}$	$I_{DS}$ (A)	$R_{GON}$ ( $\Omega$ )	$T_{RISE}$ (ns)	$T_{FALL}$ (ns)	Turn On-delay (ns)	Turn-Of delay (ns)	$E_{ON}$ ( $\mu J$ )	$E_{OFF}$ ( $\mu J$ )
-4V/+15.6V	29.2	6.8	33.6	23.2	23.0	42.76	674	88.61
	29.2	10	38.3	23.6	25.8	42.5	727.8	90.44
	29.4	12	41.04	23.44	27.8	42.95	762.7	91.59
	29.5	15	44.0	23.6	30.1	42.18	805.0	95.12
-4V/+11.7V	29.0	10	48.7	24	28.03	42.8	798.6	93.32
	29.2	6.8	44.8	23.8	27.03	43.8	777.9	94.38
	29.1	2	40.96	24.16	25.5	42.9	764.8	97.4
	29.1	1	39.2	24.3	24.0	43.1	742.3	99.59

\*Parameters:

$V_{BUS} = 750V$

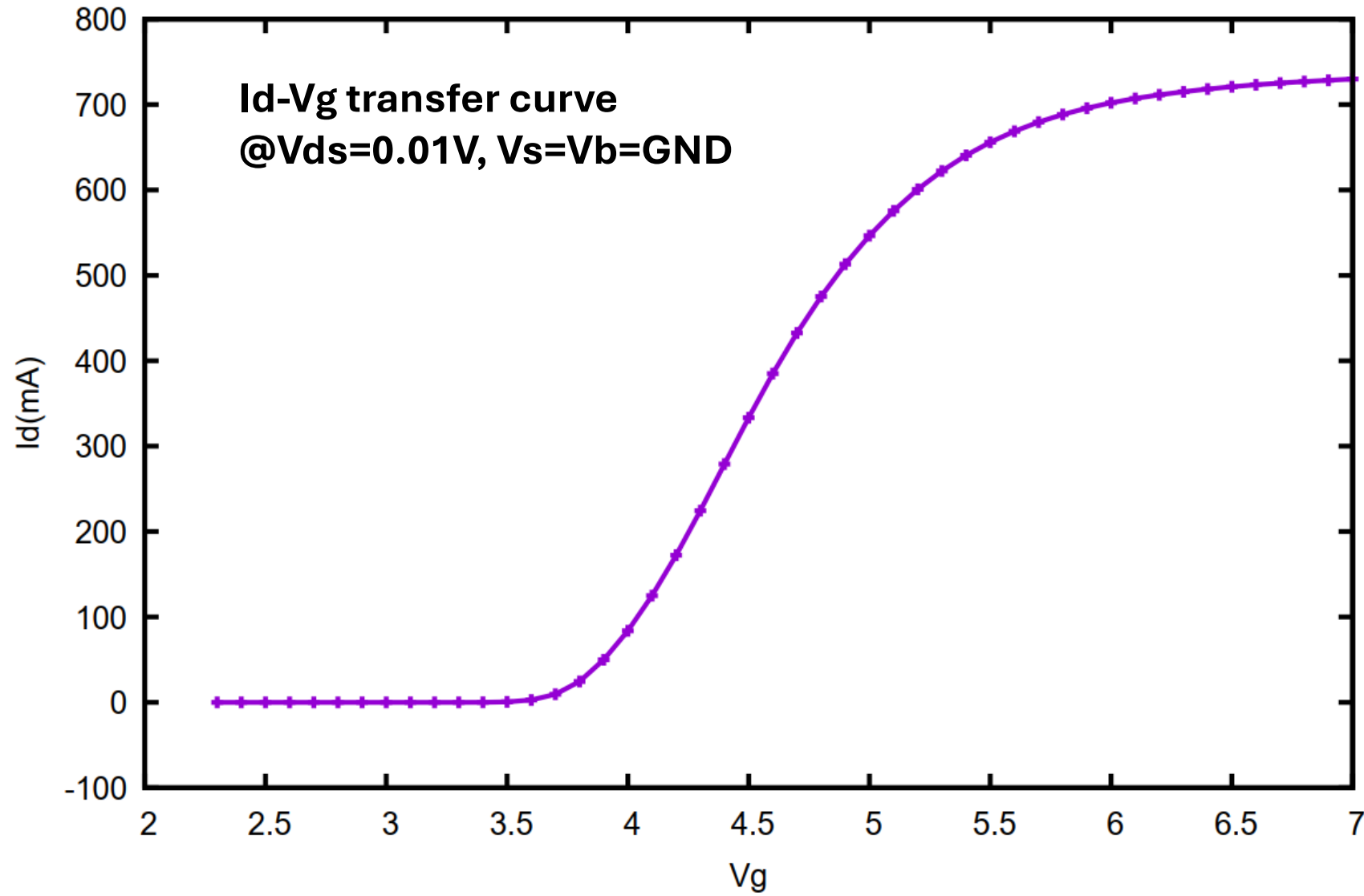
$I_{DS} = 29A$

$L = 128 \mu H$

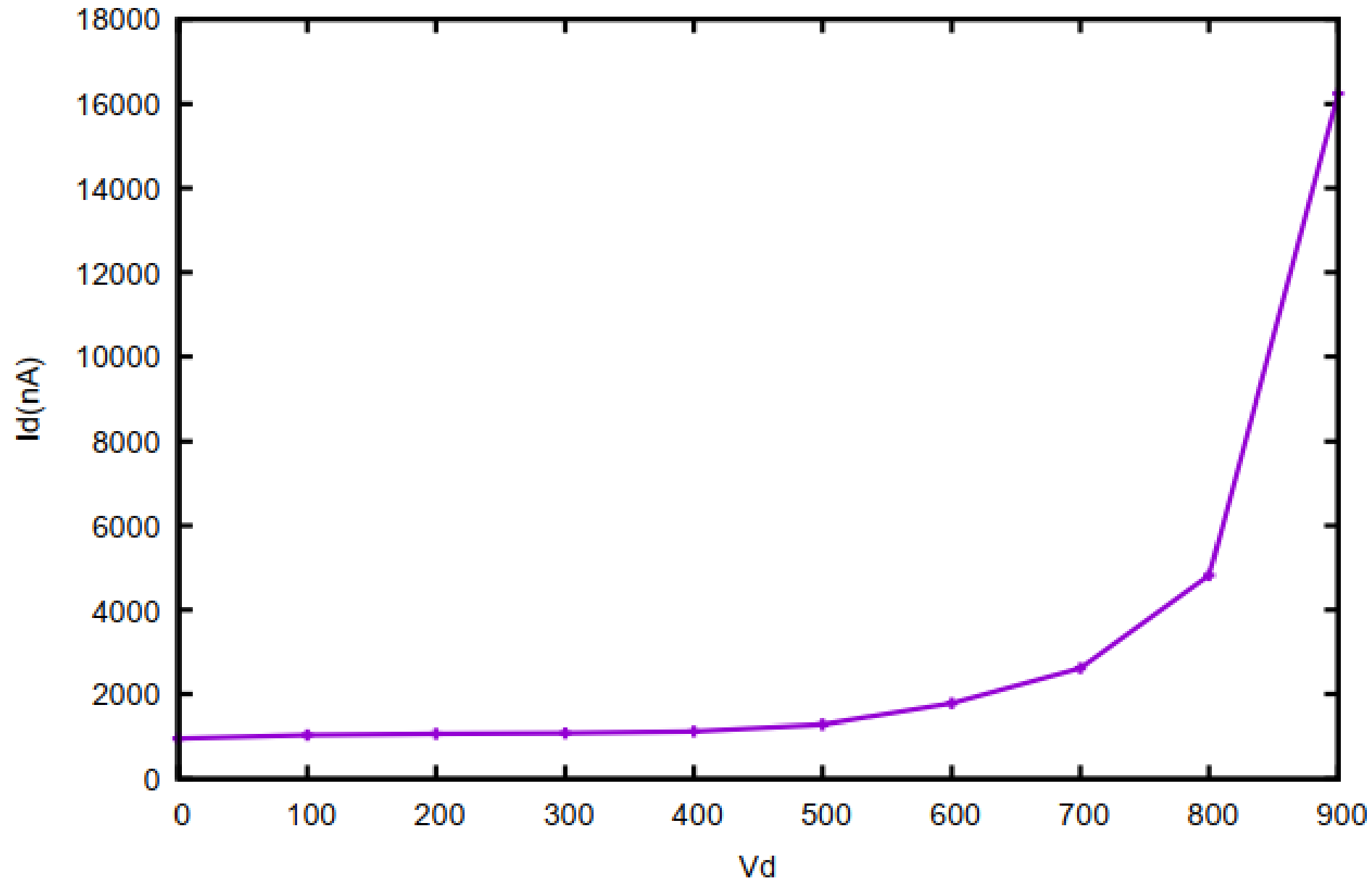
Freewheeling diode = External SiC diode (FFSH50120A)

Gate driver = Infineon IEDB7275A

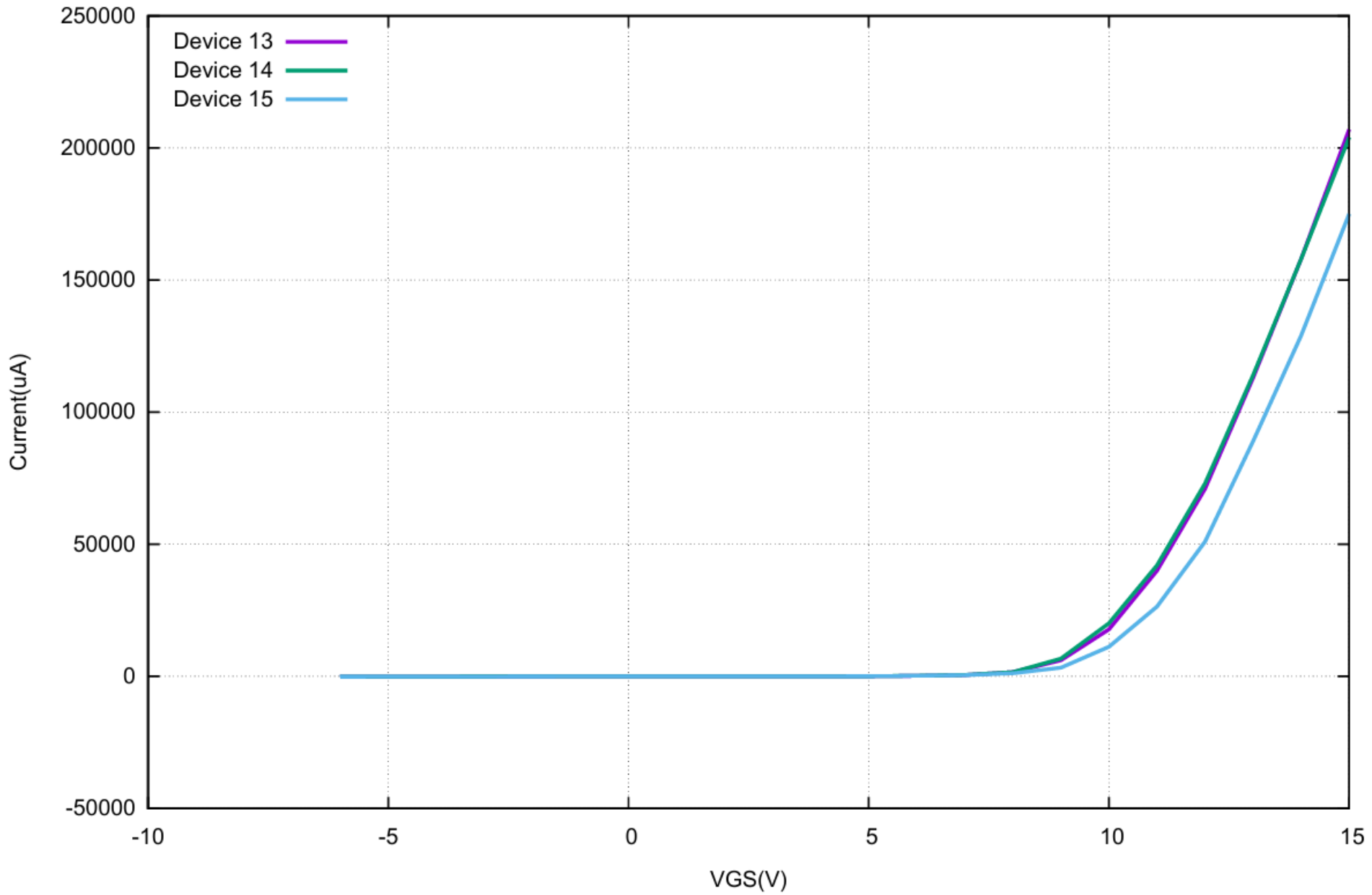
VgId03



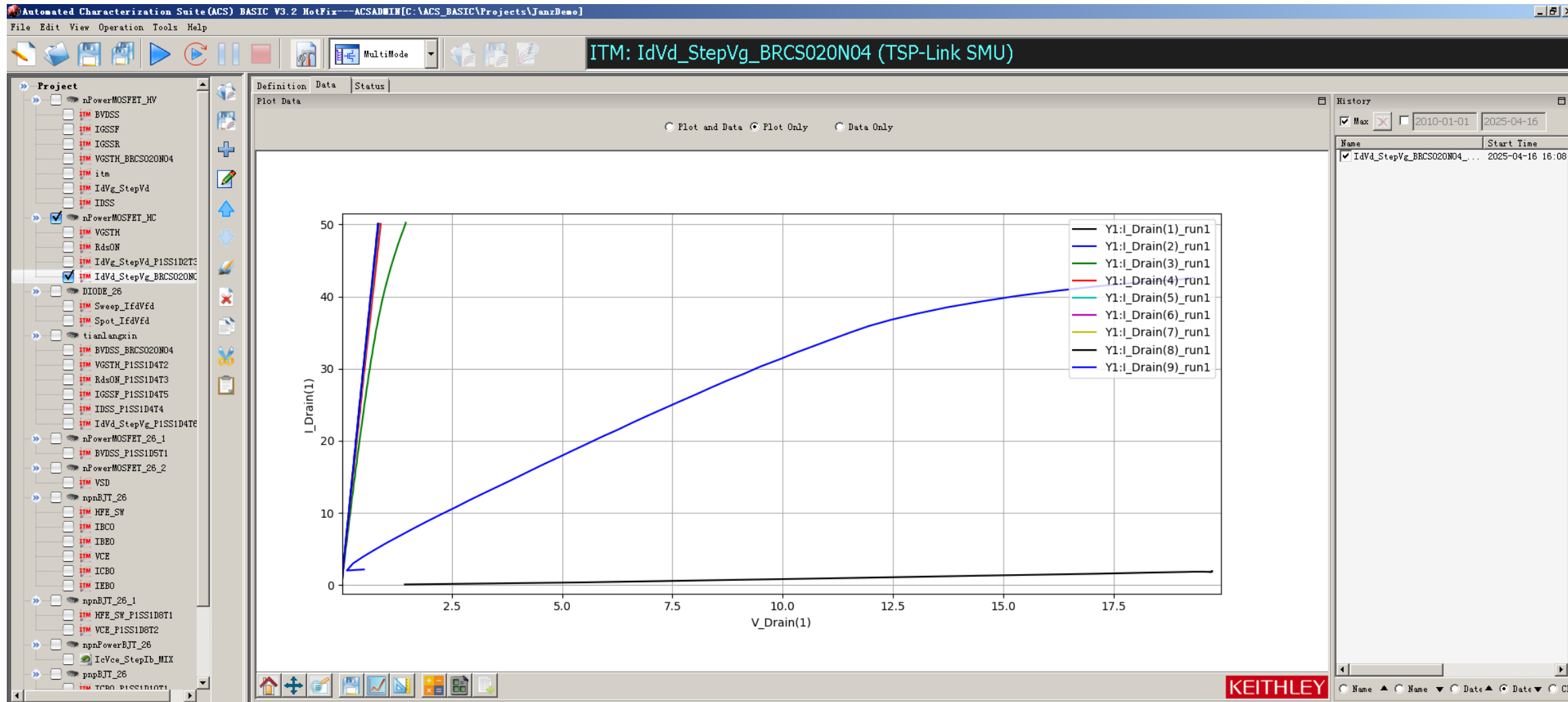
VdId01



Star120 gate leakage (TO247)



# 开态IdVds-StepVg测试结果 (电流扫描1~50A, Vgs 4~12V, 温度25°C)

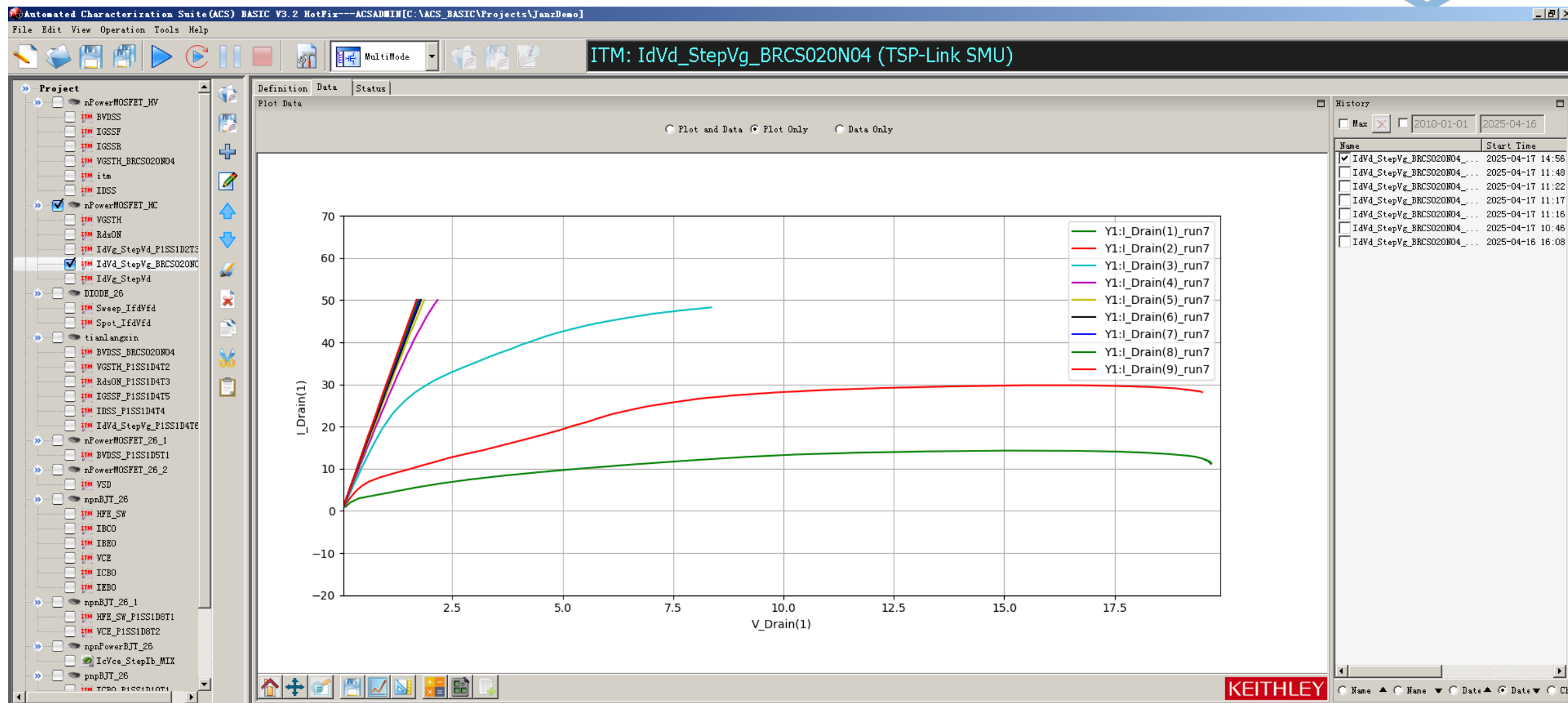


2025-04-16 16:06:02 CRITICAL SMU3 hit compliance. Test is aborted.

will expire in 28 days. Maintain service will expire in ~434 day. Current version...

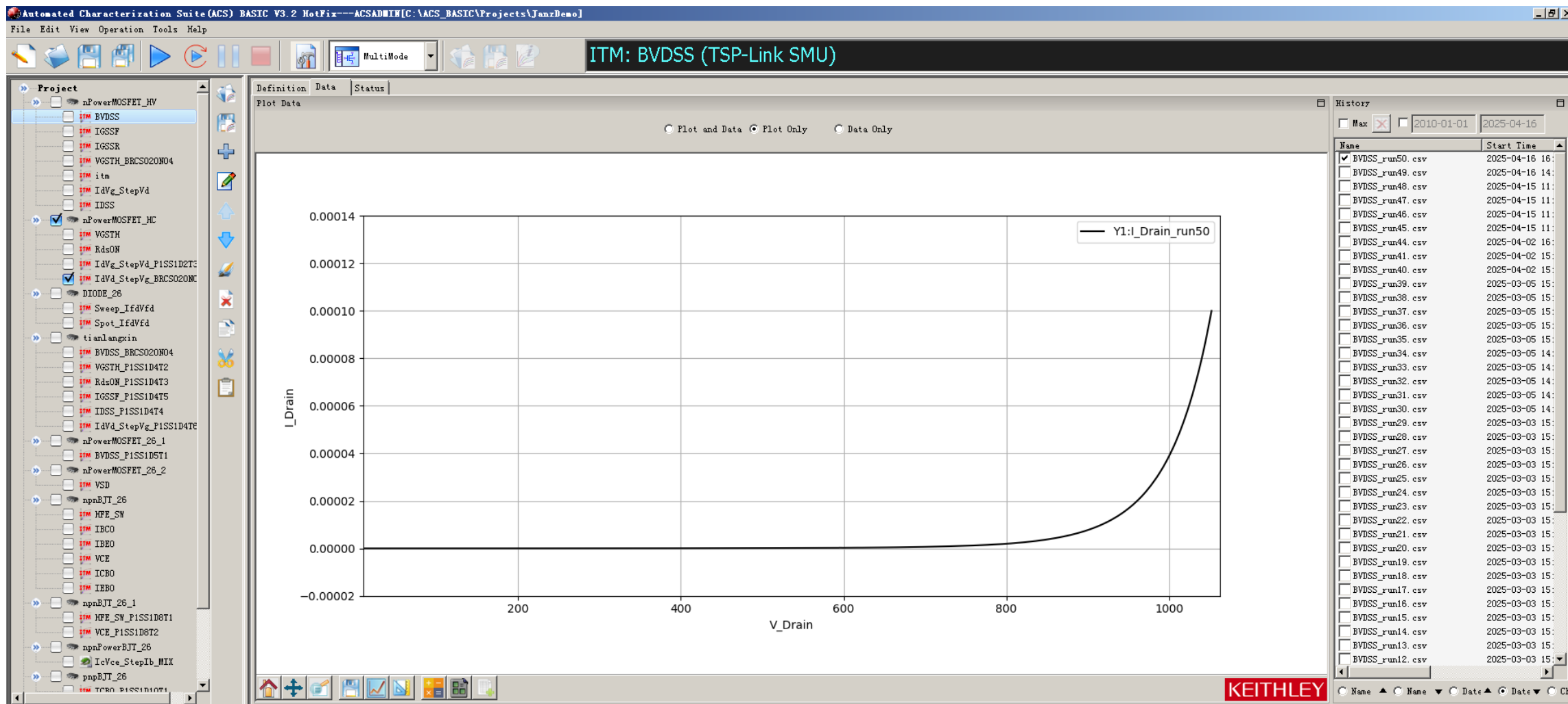
Keithley Instruments, Inc.

# 开态IdVds-StepVg测试结果 (电流扫描1~50A, Vgs 4~12V, 温度150°C)



2025-04-16 16:06:02 CRITICAL SMU3 hit compliance. Test is aborted.  
2025-04-16 17:03:48 CRITICAL SMU4 hit compliance. Test is aborted.  
2025-04-16 17:08:01 CRITICAL SMU4 hit compliance. Test is aborted.  
2025-04-16 17:08:51 CRITICAL SMU4 hit compliance. Test is aborted.  
2025-04-16 17:47:55 CRITICAL SMU4 hit compliance. Test is aborted.

# 关态的Idss-Vds (最高Vds可到900V) (扫描0~1200V, 100uA触发保护关断, 温度25°C)



2025-04-16 16:06:02 CRITICAL SMU3 hit compliance. Test is aborted.

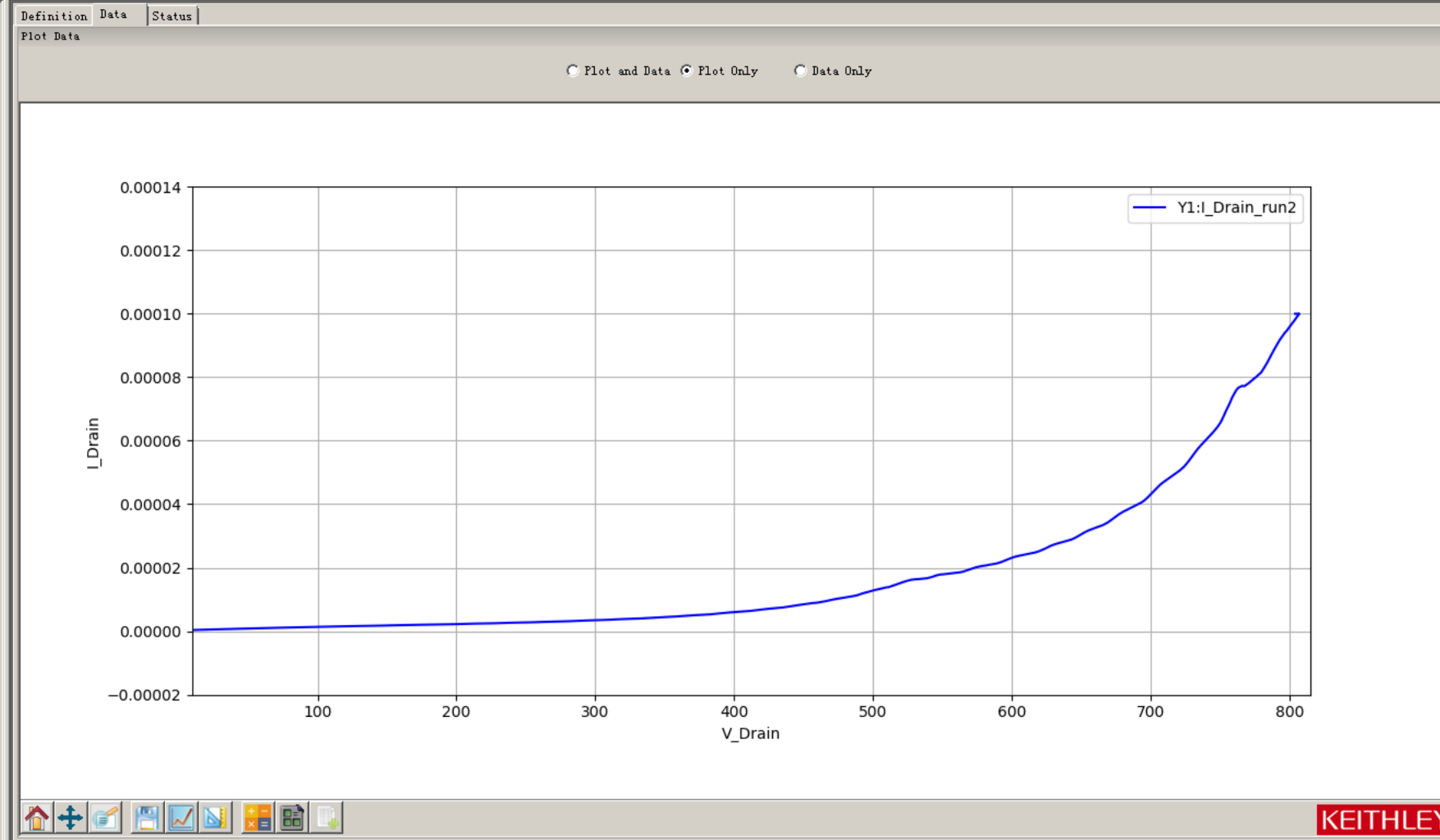
-434 day. Current version license will expire in 28 days. Maintain service will e...

Keithley Instruments, Inc.



# ITM: BVDSS (TSP-Link SMU)

- Project
  - nPowerMOSFET\_HV
    - BVDSS
    - IGSSF
    - IGSSR
    - VGSTH\_BRCS020ND4
    - itm
    - IDSS
  - nPowerMOSFET\_HC
    - VGSTH
    - RdsON
    - IdVd\_StepVd\_P1SS1D2T3
    - IdVd\_StepVg\_BRCS020ND4
    - IdVg\_StepVd
  - DIODE\_26
    - Sweep\_IfdVfd
    - Spot\_IfdVfd
  - tianlangxin
    - BVDSS\_BRCS020ND4
    - VGSTH\_P1SS1D4T2
    - RdsON\_P1SS1D4T3
    - IGSSF\_P1SS1D4T5
    - IDSS\_P1SS1D4T4
    - IdVd\_StepVg\_P1SS1D4T5
  - nPowerMOSFET\_26\_1
    - BVDSS\_P1SS1D5T1
  - nPowerMOSFET\_26\_2
    - VSD
  - npnBJT\_26
    - HFE\_SW
    - IBCO
    - IBEO
    - VCE
    - ICB0
    - IEBO
  - npnBJT\_26\_1
    - HFE\_SW\_P1SS1D8T1
    - VCE\_P1SS1D8T2
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    - IcVce\_StepIb\_MIX
  - pnpBJT\_26
    - ICR\_P1SS1D10T1



History

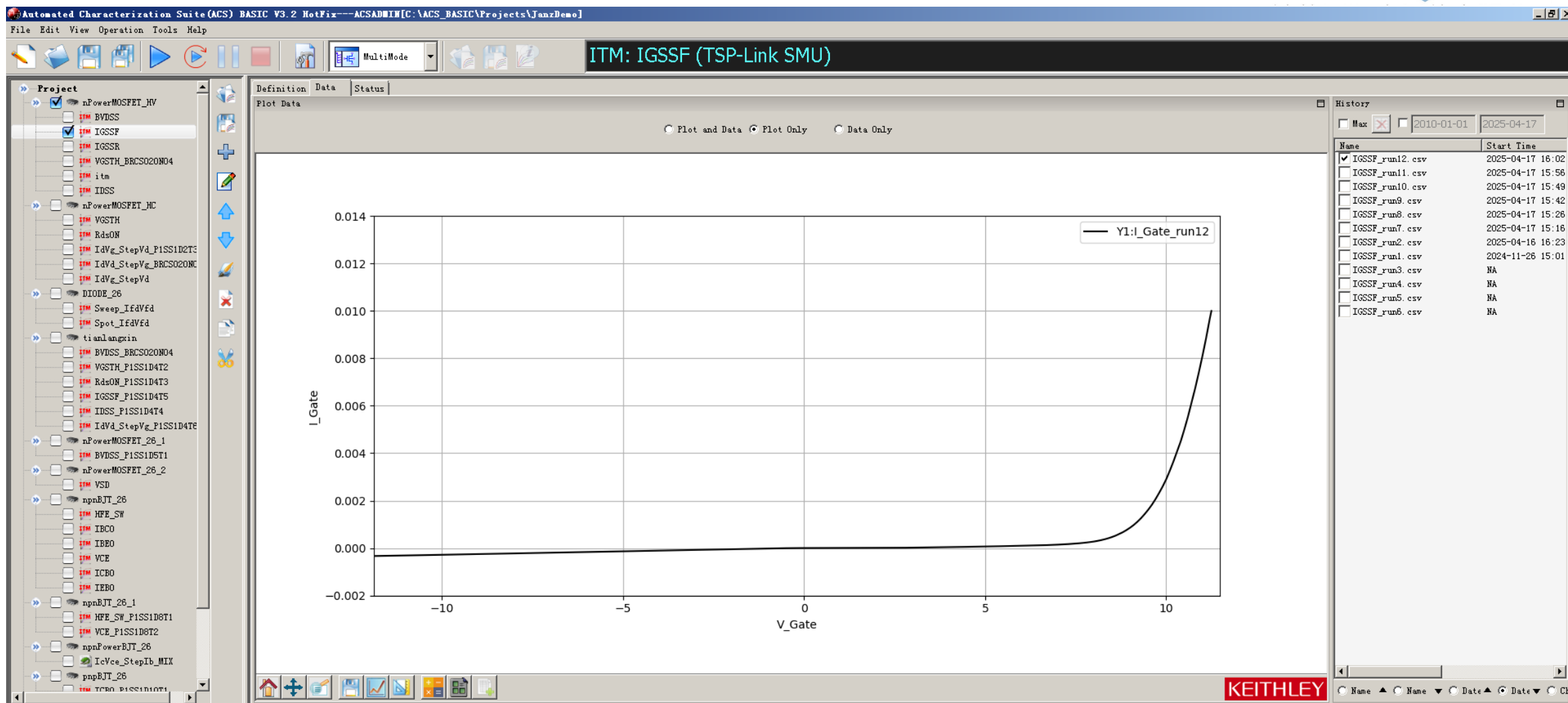
Max  2010-01-01 2025-04-17

Name	Start Time
<input checked="" type="checkbox"/> BVDSS_run2.csv	2025-04-17 15:35
<input type="checkbox"/> BVDSS_run1.csv	2025-04-17 15:33

2025-04-17 15:24:42 CRITICAL SMU2 hit compliance. Test is aborted.  
 2025-04-17 15:30:40 CRITICAL SMU2 hit compliance. Test is aborted.  
 2025-04-17 15:33:23 CRITICAL BVDSS Hit max history, backup all history files.  
 2025-04-17 15:34:49 CRITICAL SMU3 hit compliance. Test is aborted.  
 2025-04-17 15:37:00 CRITICAL SMU3 hit compliance. Test is aborted.



# Ig-Vg曲线 (Vgs=-12 to 12V, Igss限流10mA, Vds = 0V, 温度25°C)



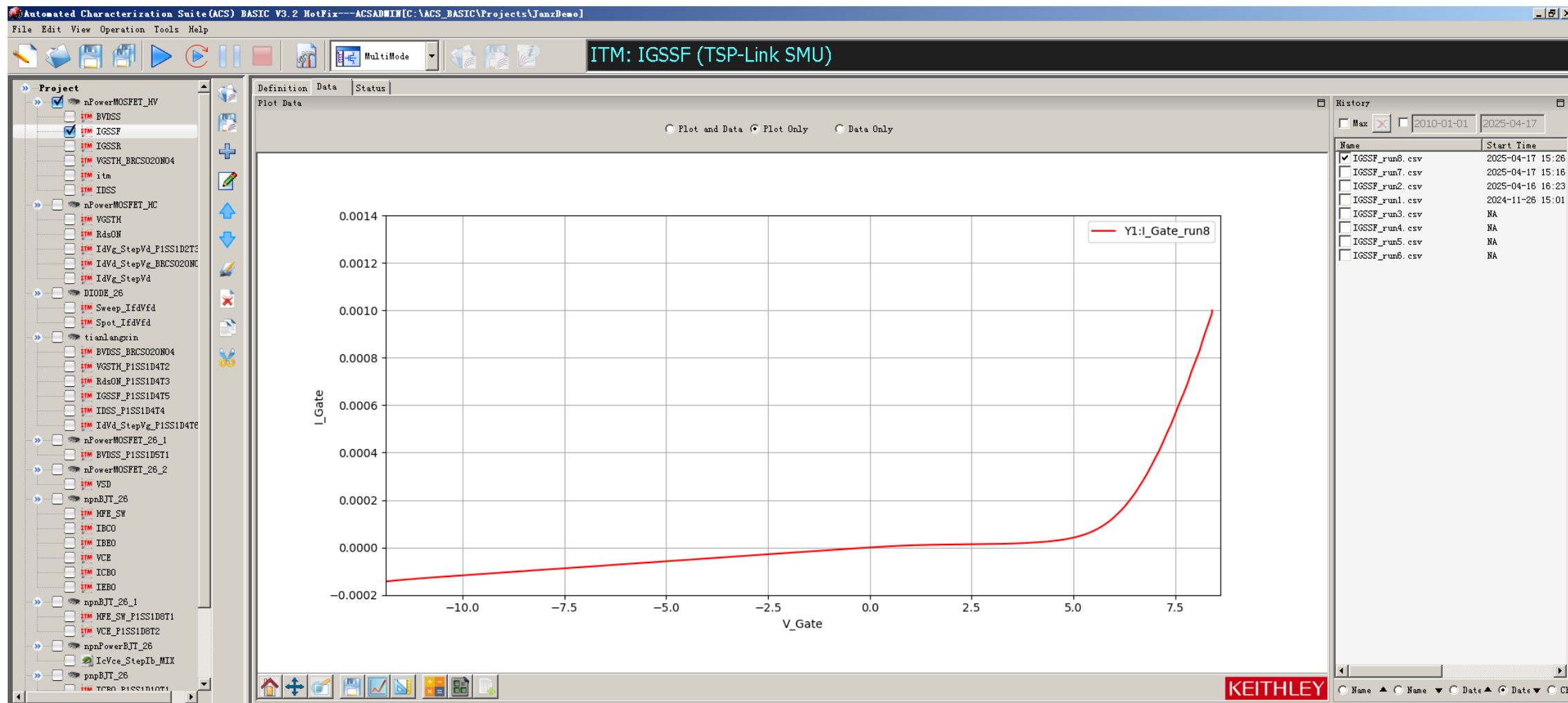
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2025-04-17 15:33:23 CRITICAL BVDSS Hit max history, backup all history files.  
2025-04-17 15:34:49 CRITICAL SMU3 hit compliance. Test is aborted.  
2025-04-17 15:37:00 CRITICAL SMU3 hit compliance. Test is aborted.  
2025-04-17 15:46:19 CRITICAL SMU2 hit compliance. Test is aborted.  
2025-04-17 15:52:55 CRITICAL SMU2 hit compliance. Test is aborted.  
2025-04-17 16:00:41 CRITICAL SMU2 hit compliance. Test is aborted.  
2025-04-17 16:06:57 CRITICAL SMU2 hit compliance. Test is aborted.

ire in 27 days. Maintain service will expire in -435 day. Current version license ...

Keithley Instruments, Inc.

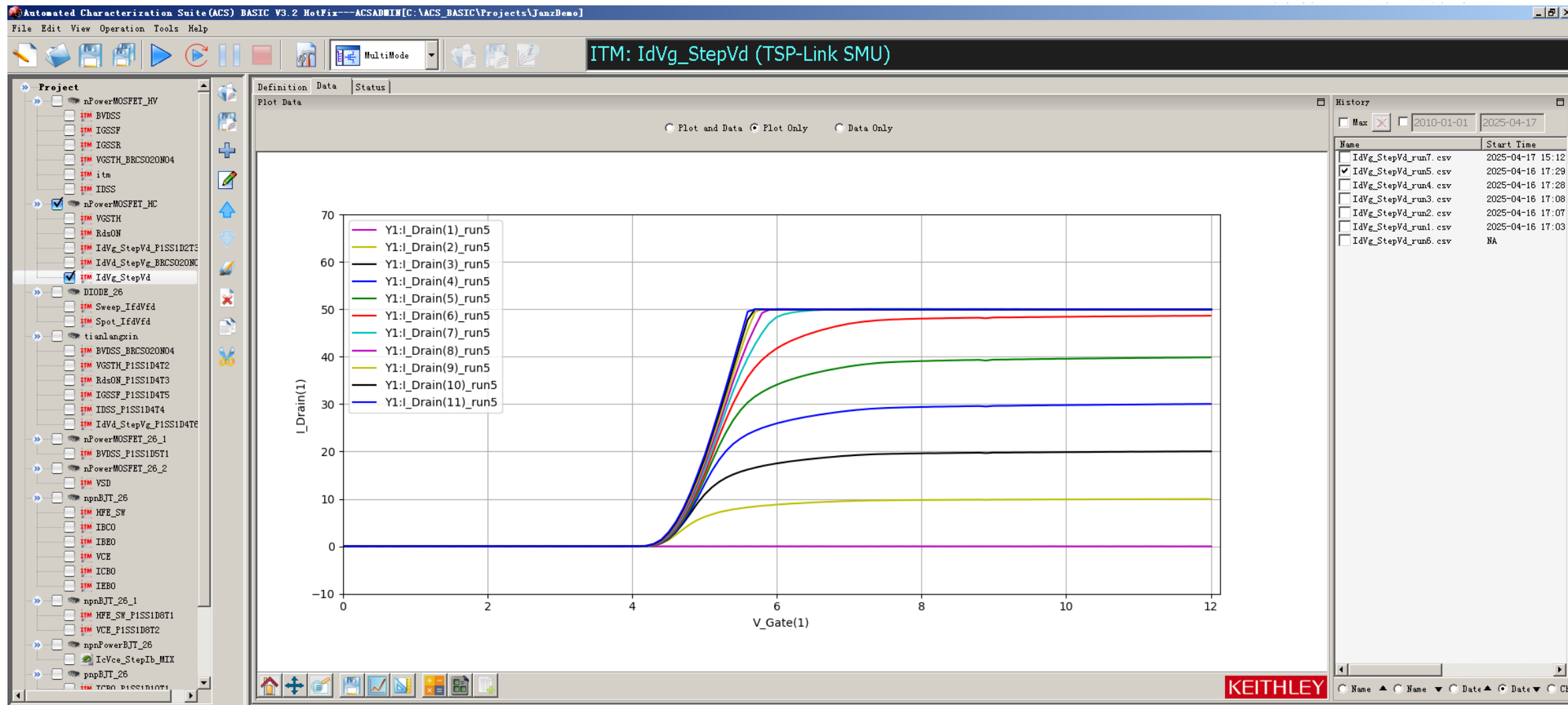


# Ig-Vg曲线 (Vgs=-12 to 12V, Igss限流1mA, Vds = 0V, 温度150°C)

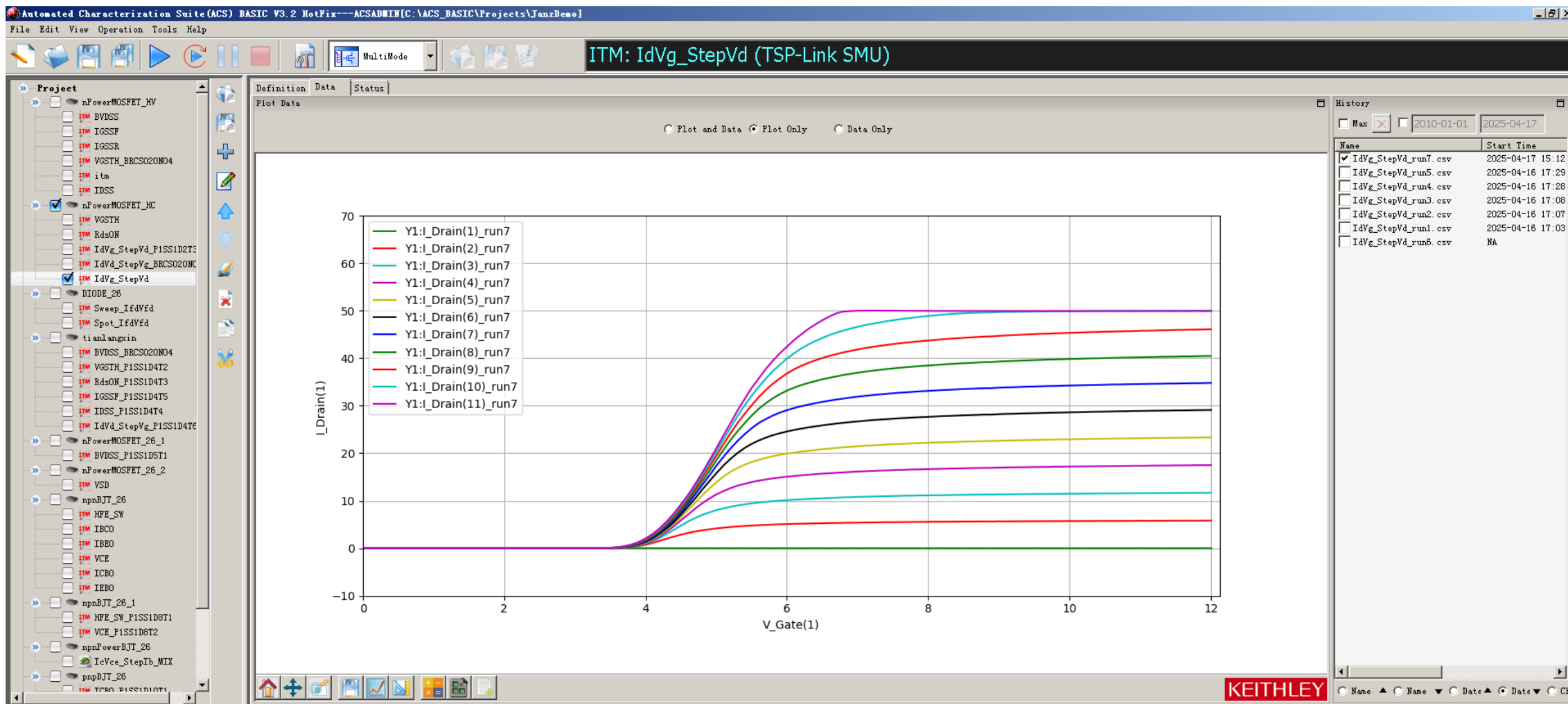


2025-04-17 15:24:42 CRITICAL SMU2 hit compliance. Test is aborted.  
2025-04-17 15:30:40 CRITICAL SMU2 hit compliance. Test is aborted.

# Id-Vg曲线 (Vgs=0-12V, Vds=0~2V, Id=0~50A, 温度25°C)



# Id-Vg曲线 (Vgs=0-12V, Vds=0~2V, Id=0~50A, 温度150°C)

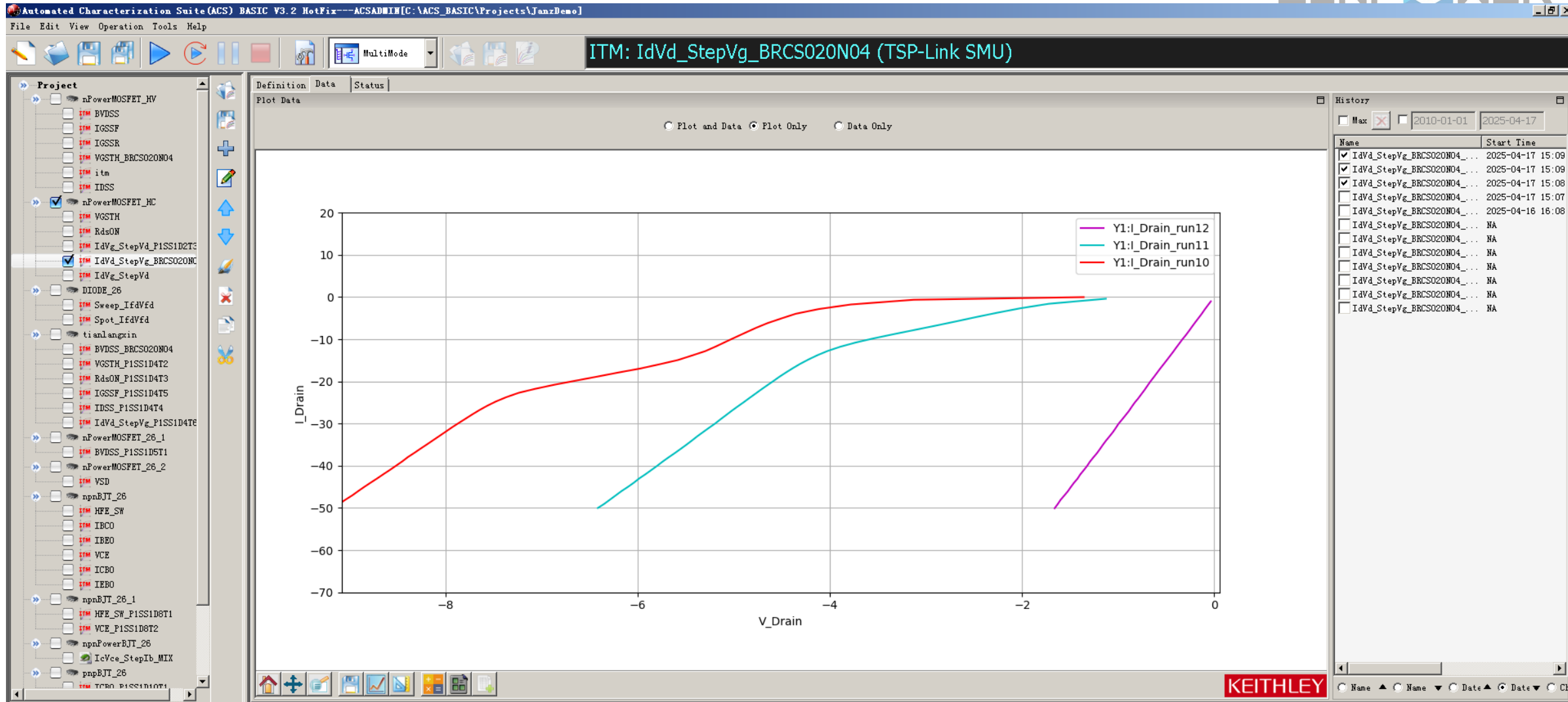


# 反向导通的Isd-Vsd (Vgs=-3V/0V/12V, 温度25°C)



2025-04-16 16:06:02 CRITICAL SMU3 hit compliance. Test is aborted.  
2025-04-16 17:03:48 CRITICAL SMU4 hit compliance. Test is aborted.  
2025-04-16 17:08:01 CRITICAL SMU4 hit compliance. Test is aborted.  
2025-04-16 17:08:51 CRITICAL SMU4 hit compliance. Test is aborted.  
2025-04-16 17:47:55 CRITICAL SMU4 hit compliance. Test is aborted.

# 反向导通的Isd-Vsd ( $V_{gs}=-3V/0V/12V$ , 温度 $150^{\circ}C$ )



# Content

Basic wafer info/DC data

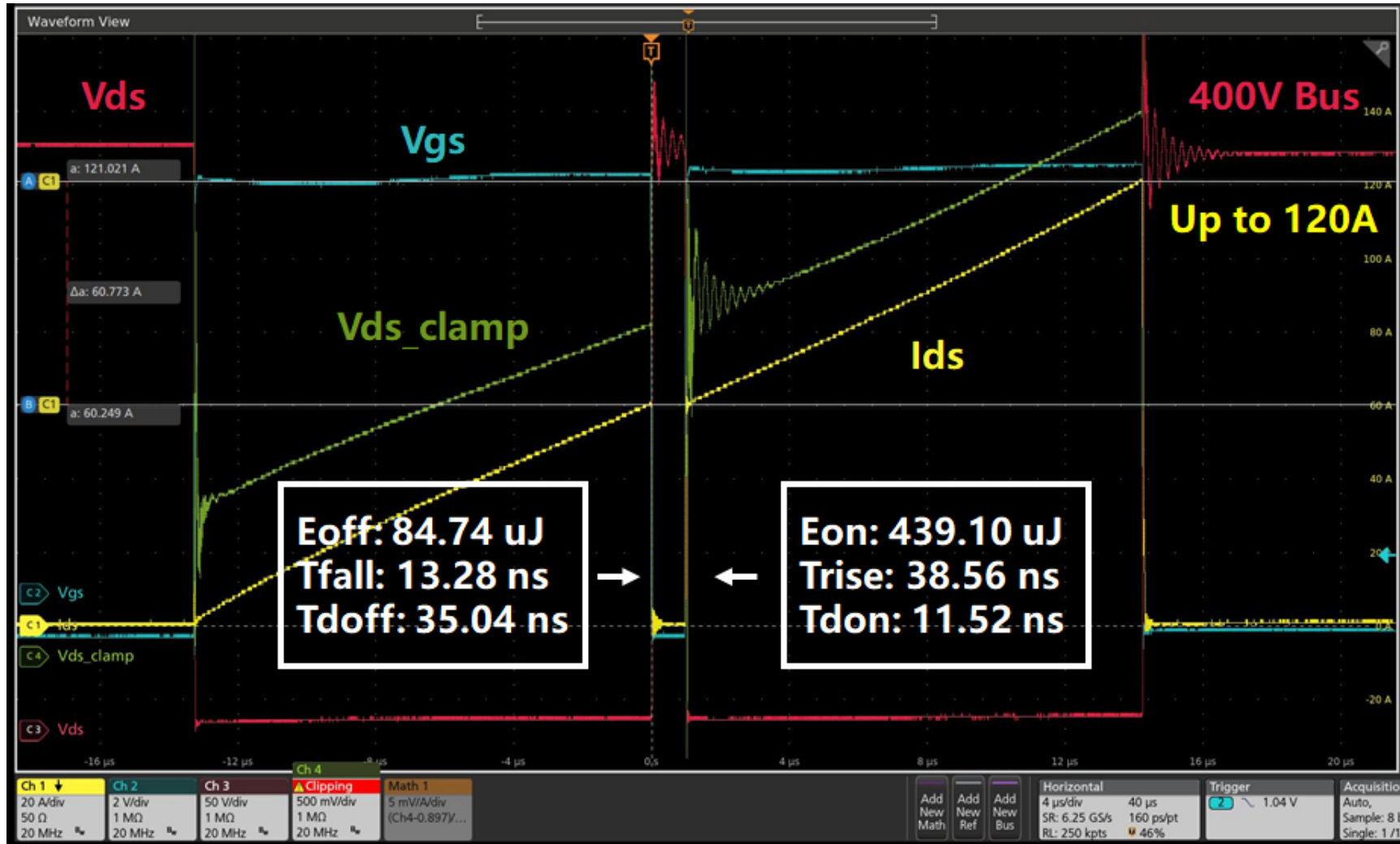


Dynamic test data

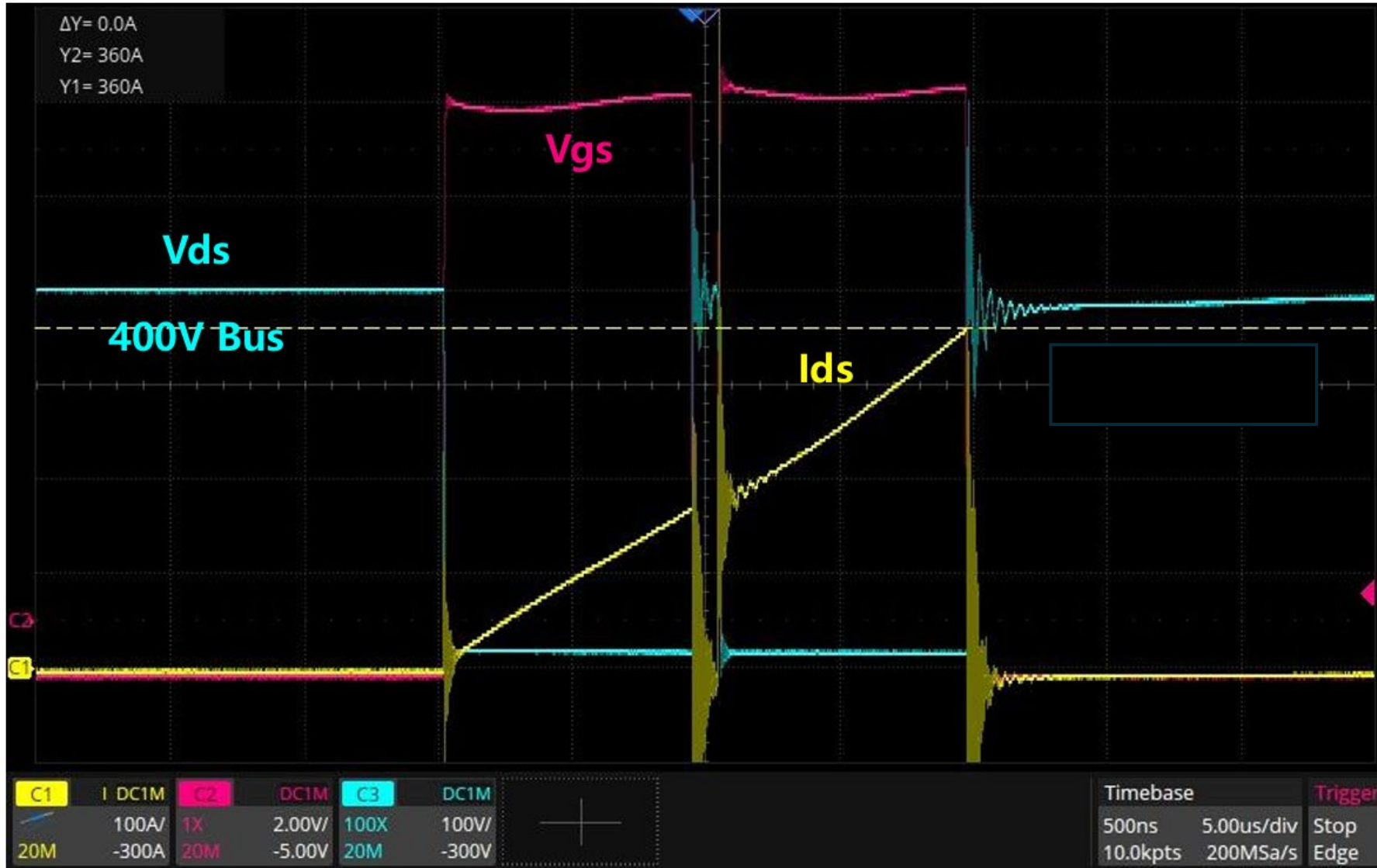
Chip probe data

App notes

# TO247-4 DPT Waveform



# 3-parallel TO247-4 DPT Waveform (> 360A)



## Gate pulsing test at 200KHz (4 uS on /1 uS off)

VG1(-)	VG1(+)	VG0(-)	VG0(+)	VBUS
-1.3	11.6	-0.7	7.4	0
-3.4	11.6	-3.1	7.4	0
-6.3	11.6	-6.3	7.4	0
-3.4	11.6	-3.0	7.4	100V (1.5A)
-3.4	11.6	-2.9	7.4	200V (2.1A)
-3.4	11.6	-2.8	7.4	400V (4.5A)

# Content

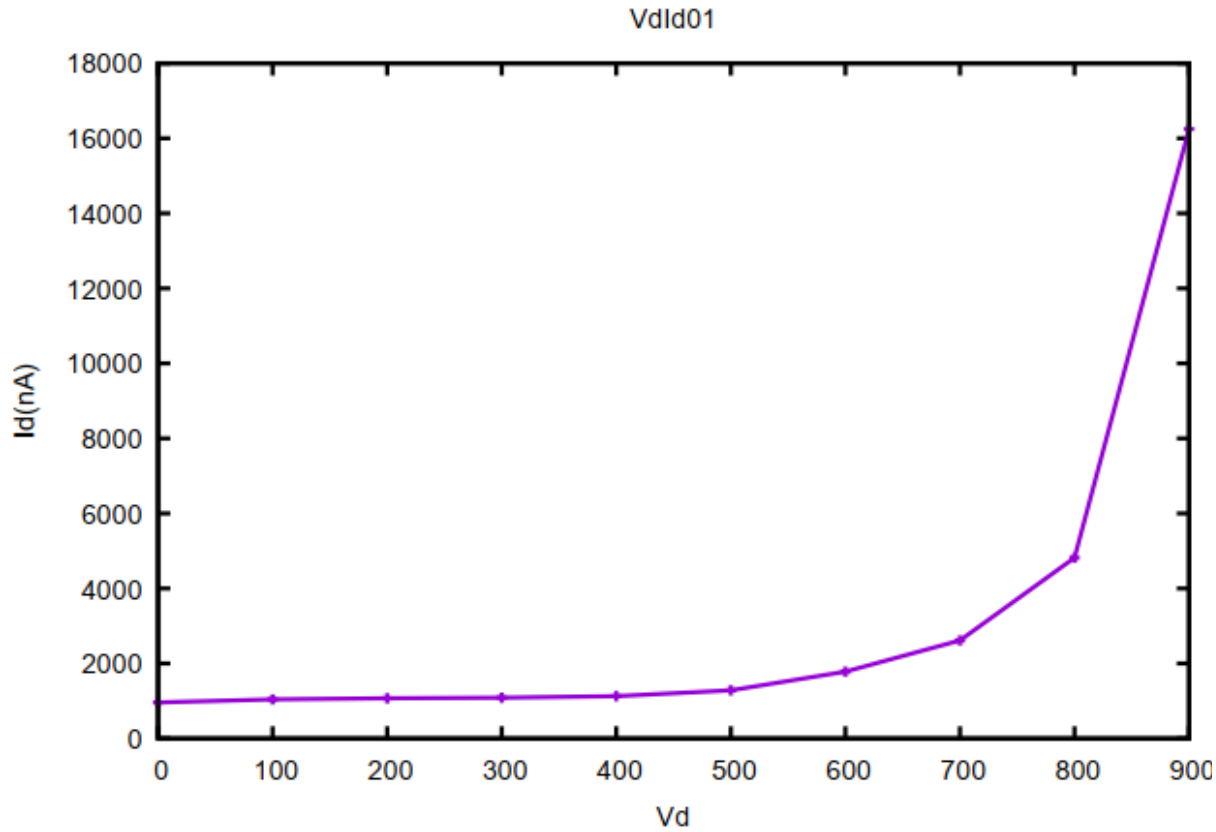
Basic wafer info/DC data

Dynamic test data

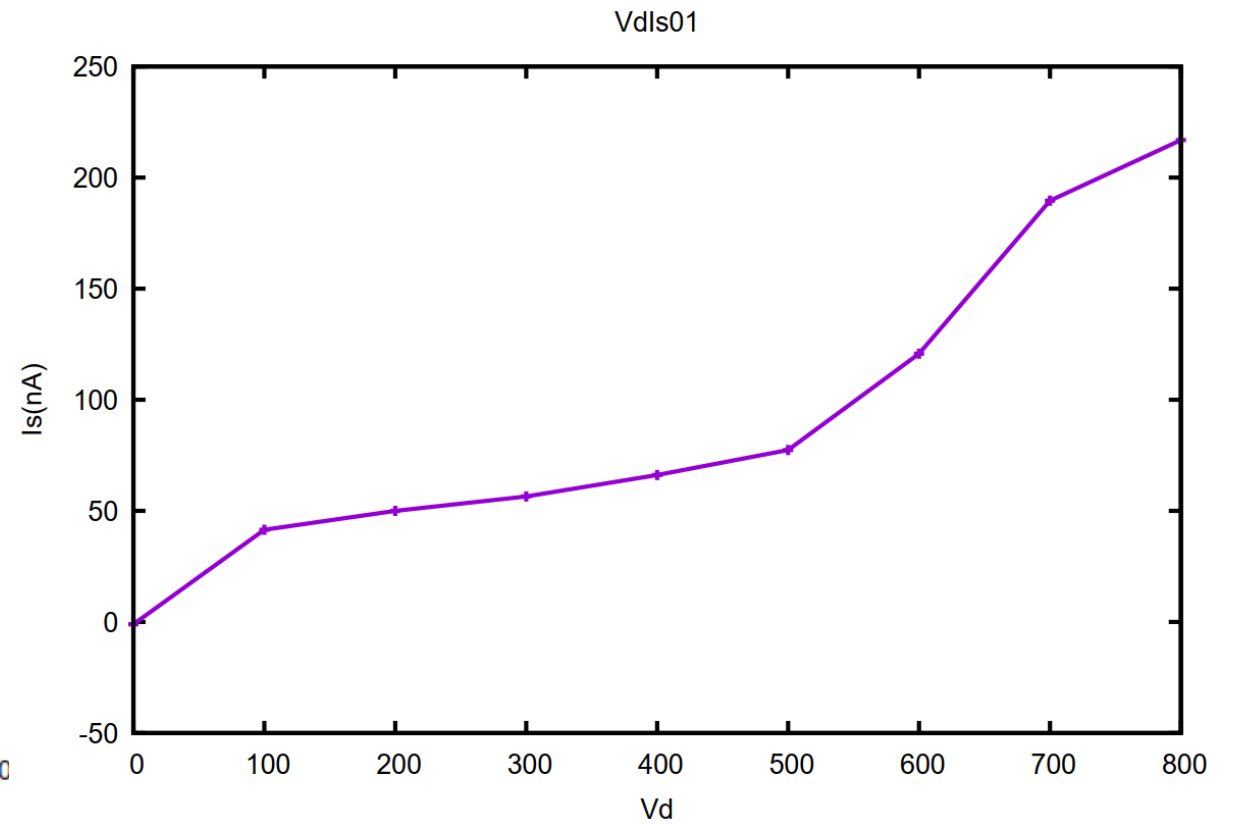
➔ Chip probe data

App notes

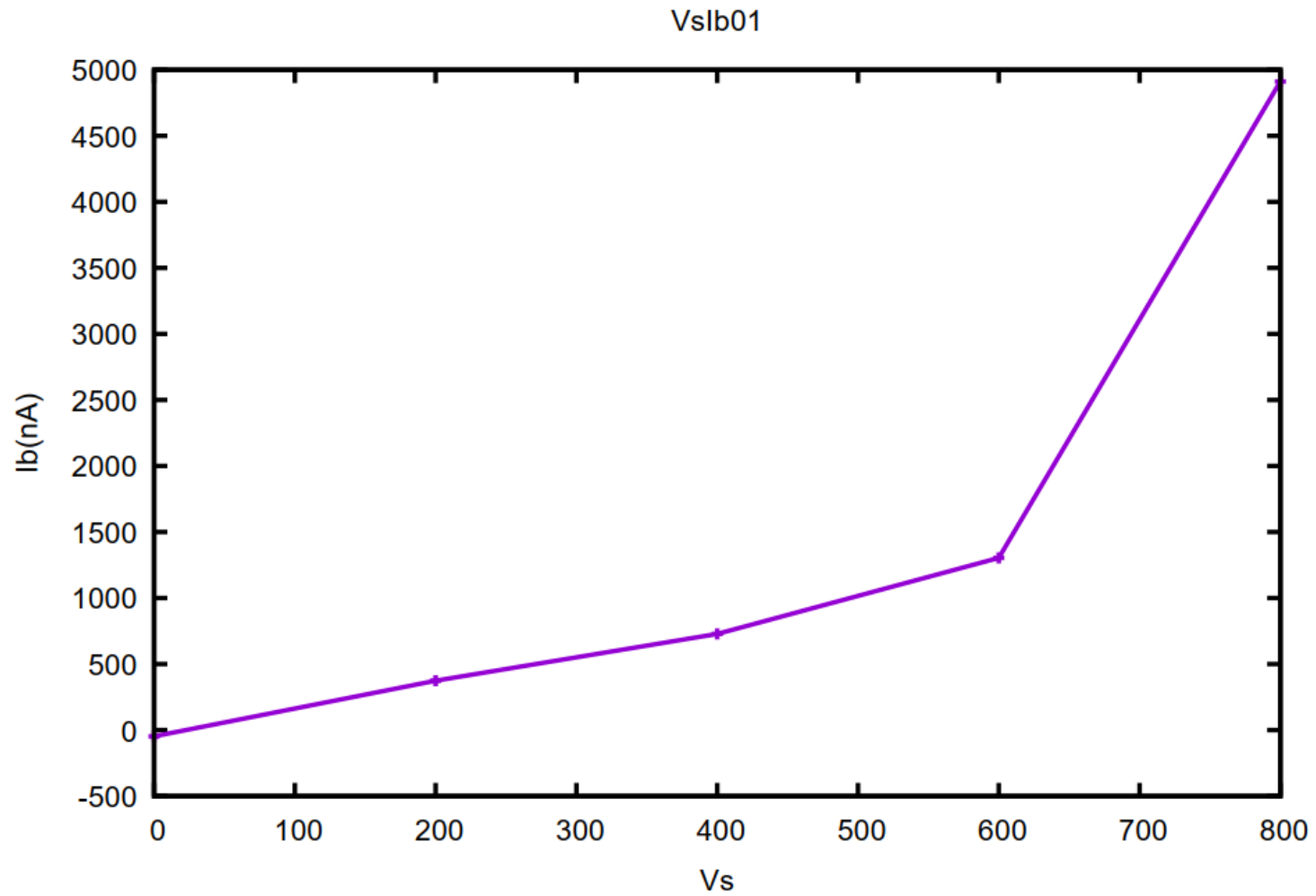
# @RT



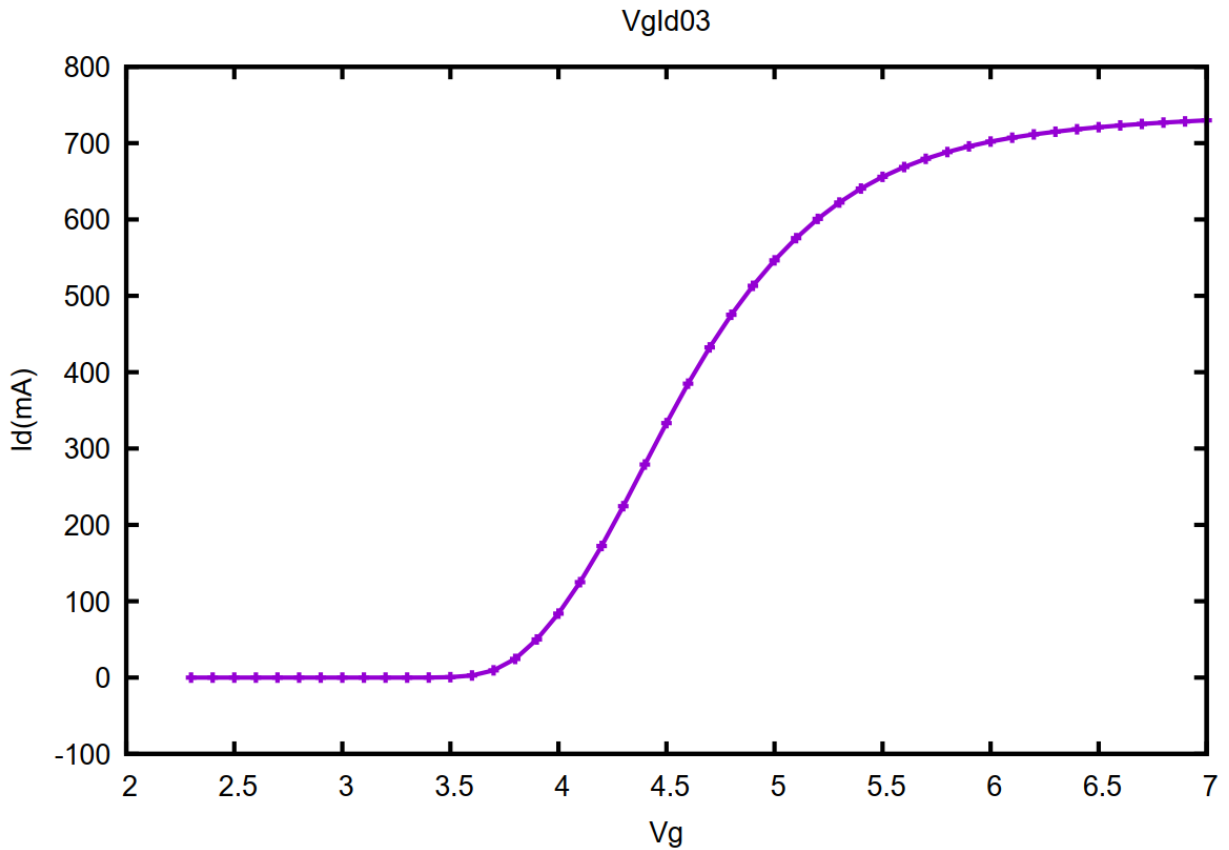
**Drain leakage  $I_{dss}$  versus  $V_{ds}$   
@ $V_g=V_s=V_b=GND$**



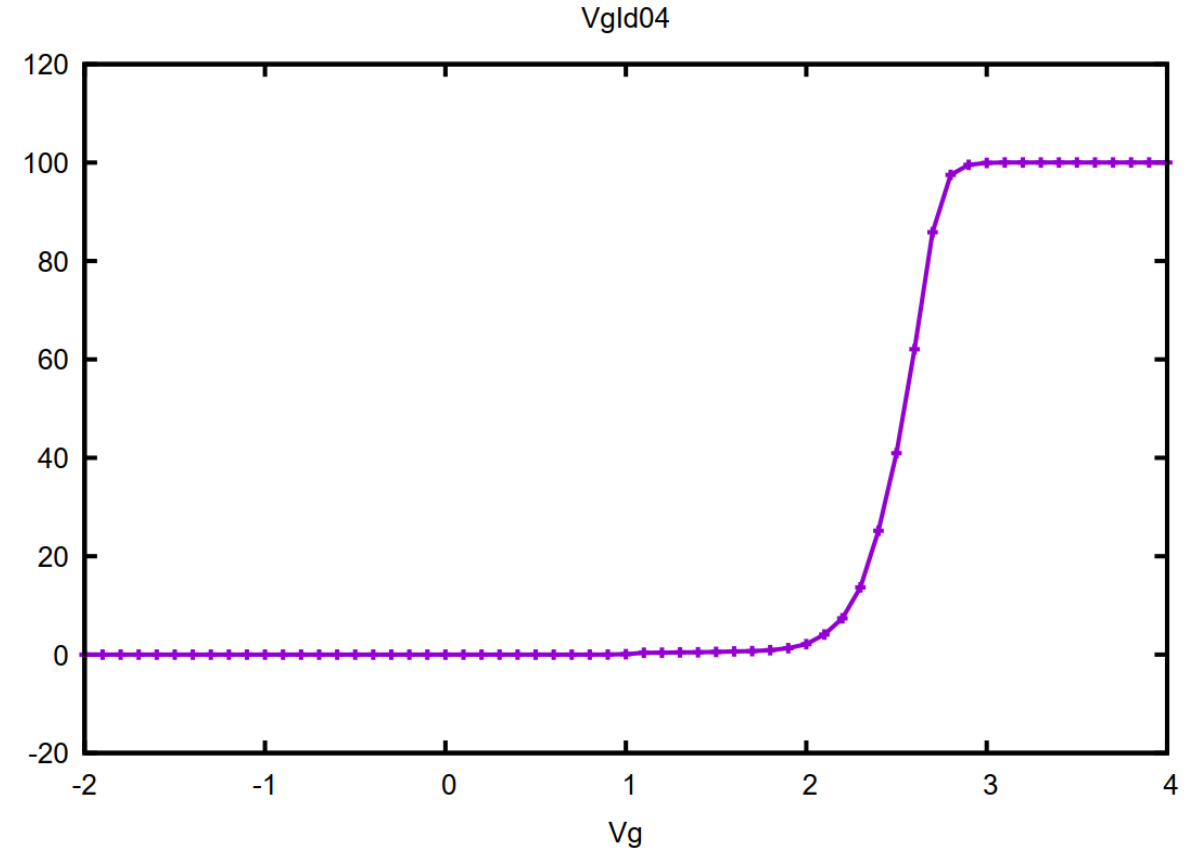
**Source leakage  $I_s$  versus  $V_{ds}$   
@ $V_g=V_s=V_b=GND$**



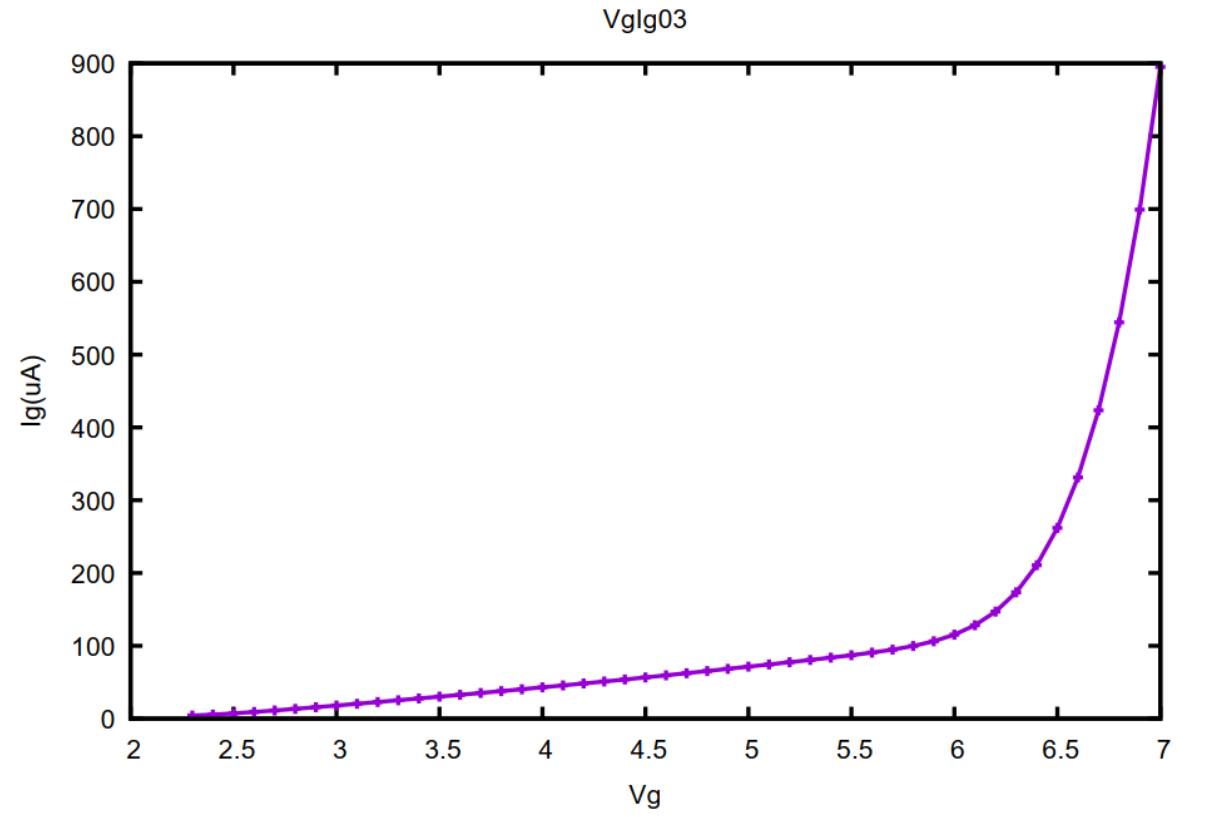
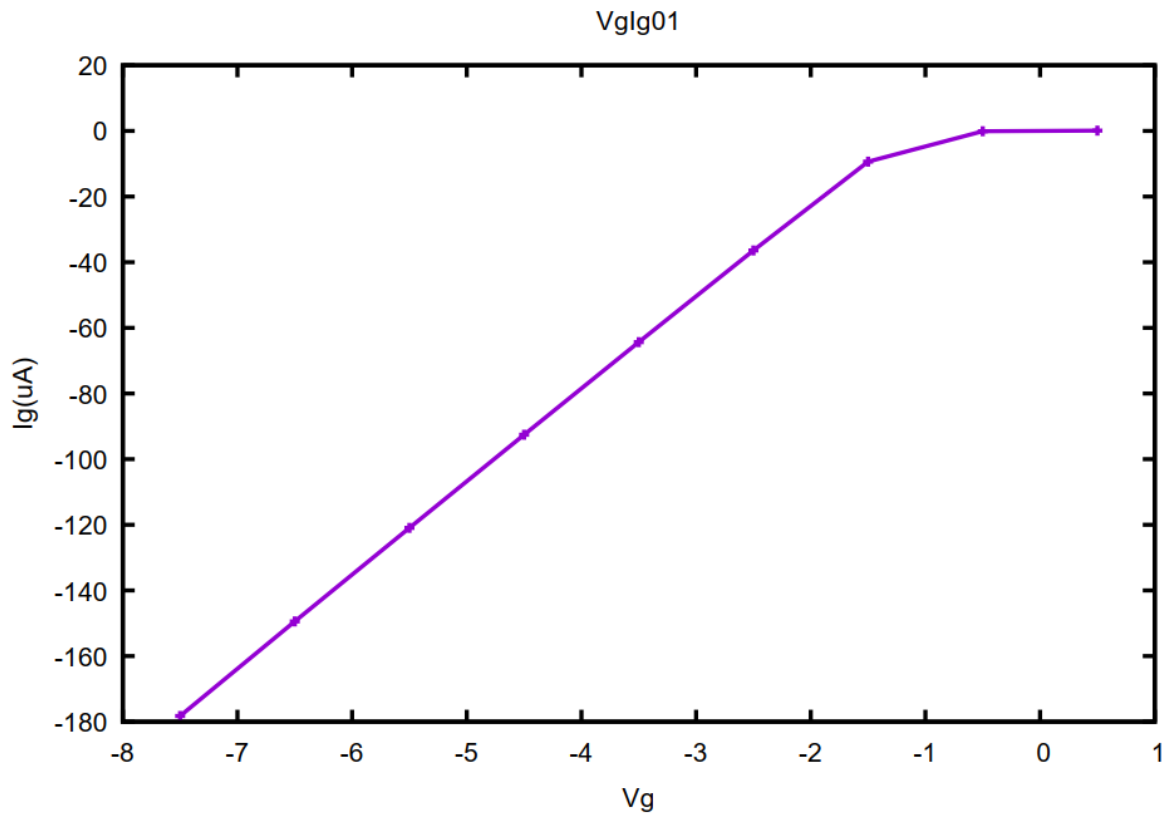
**Bulk (Substrate) leakage  $I_b$  versus  $V_s$   
@ $V_g=V_s=V_d$ , B=GND**



**Id-Vg transfer curve  
@Vds=0.01V, Vs=Vb=GND**

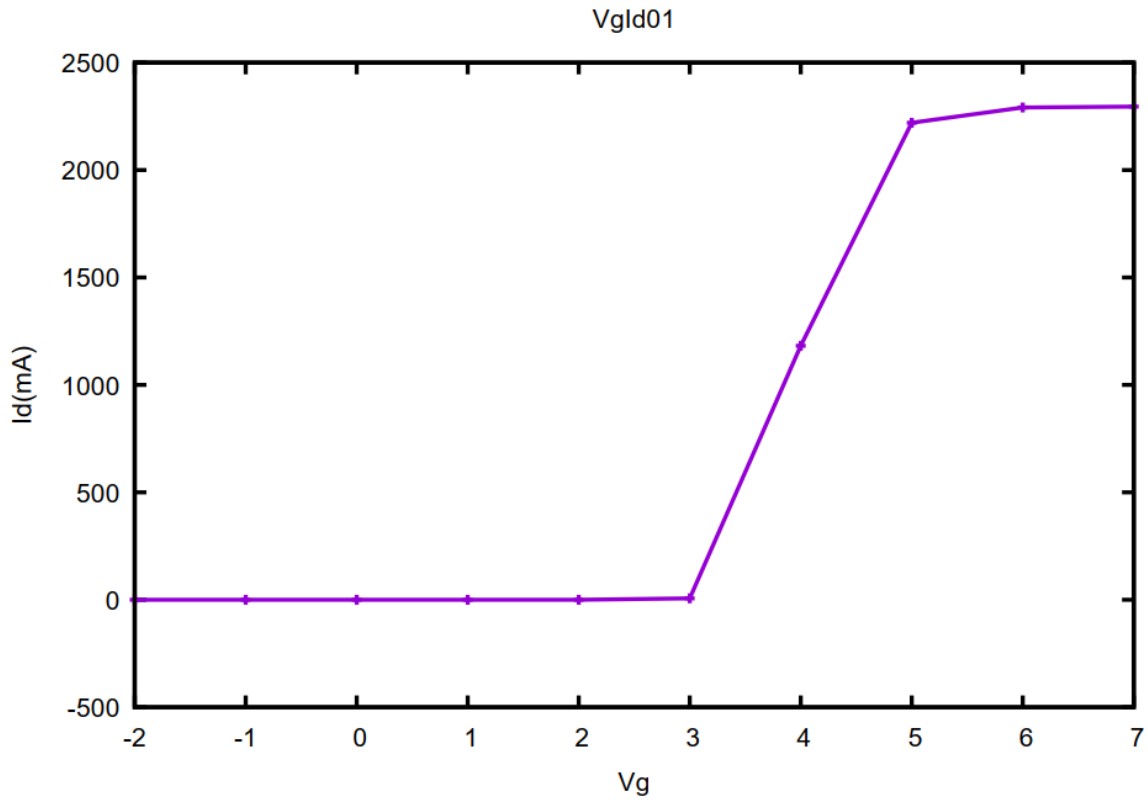


**Id vs Vg transfer curve  
@Vds=100V, Vs=Vb=GND**

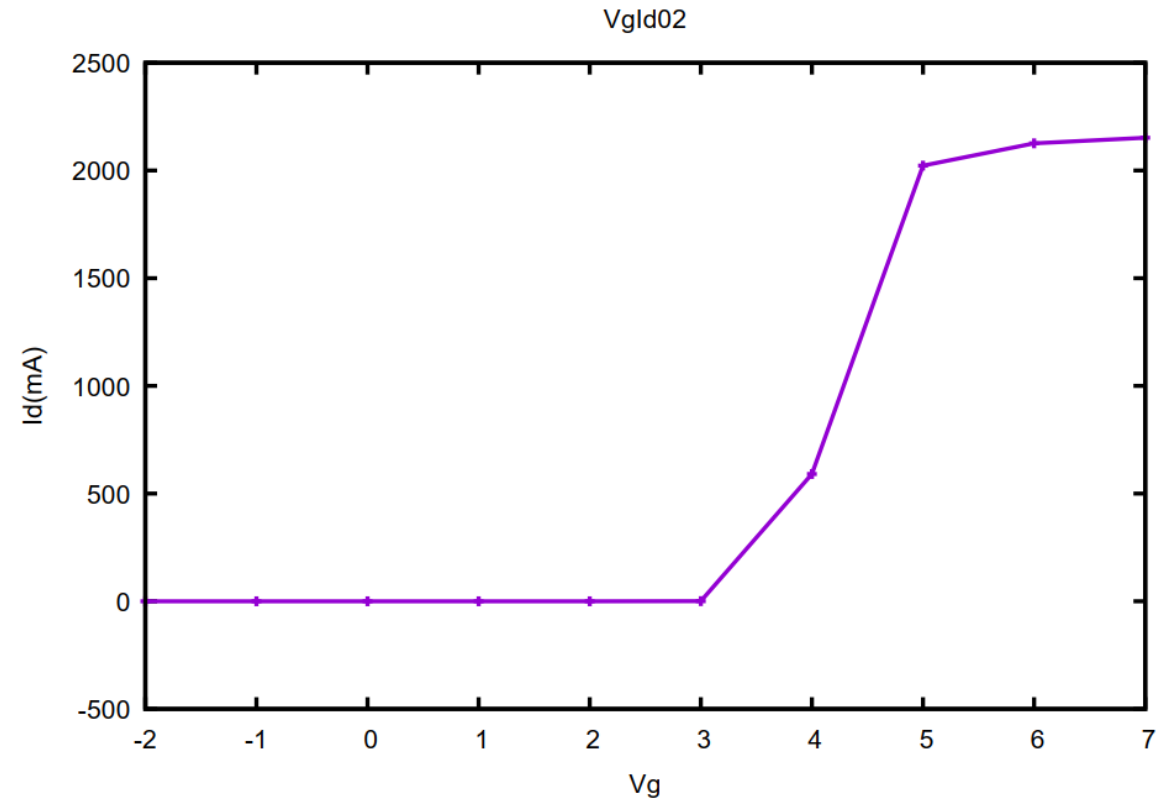


**Gate leakage**  
**@ $V_{ds}=0.1\text{V}$ ,  $V_s=V_b=\text{GND}$**

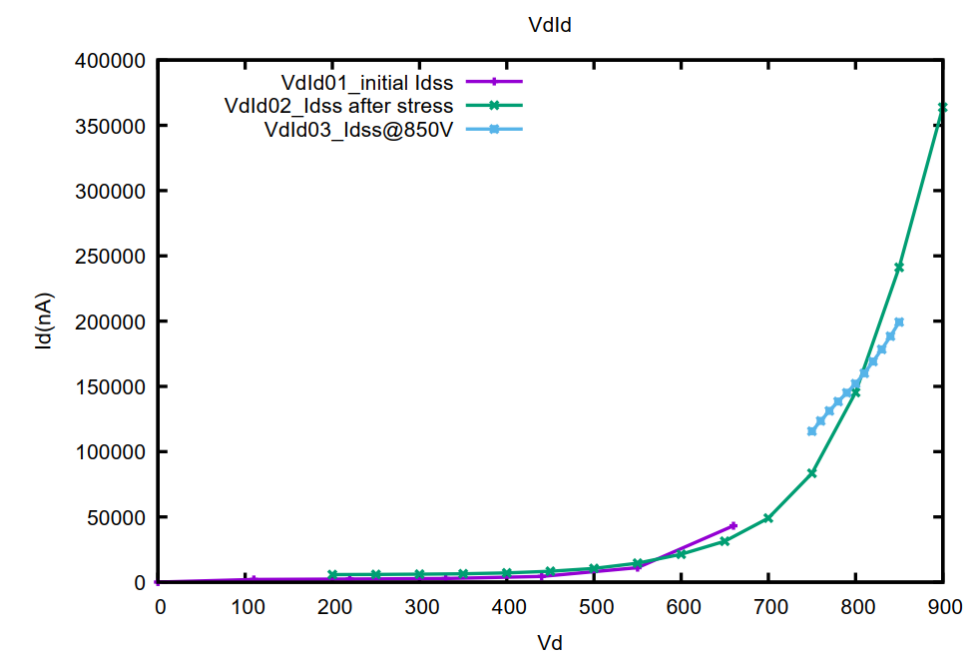
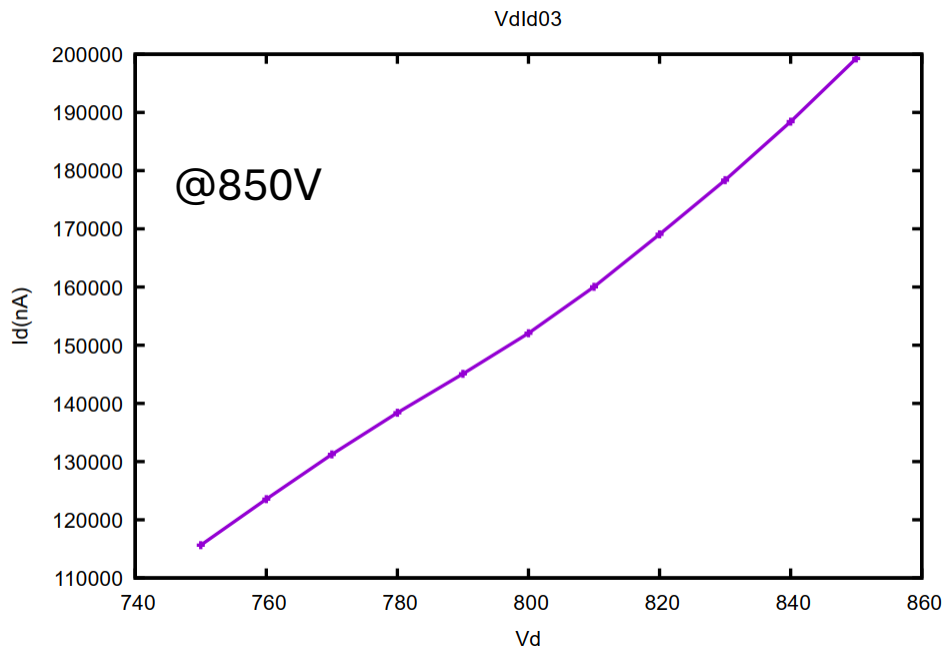
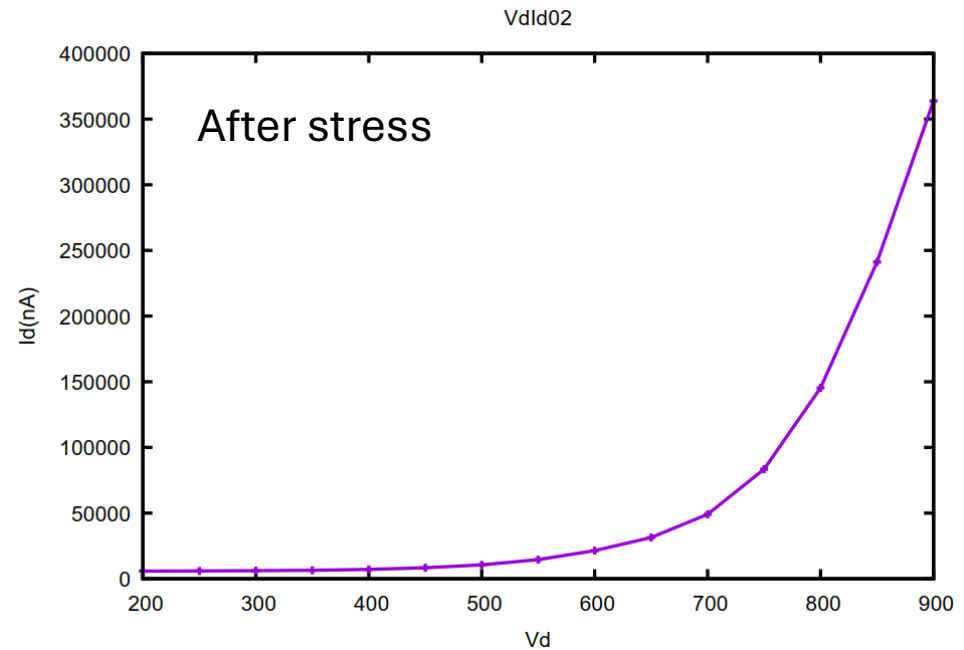
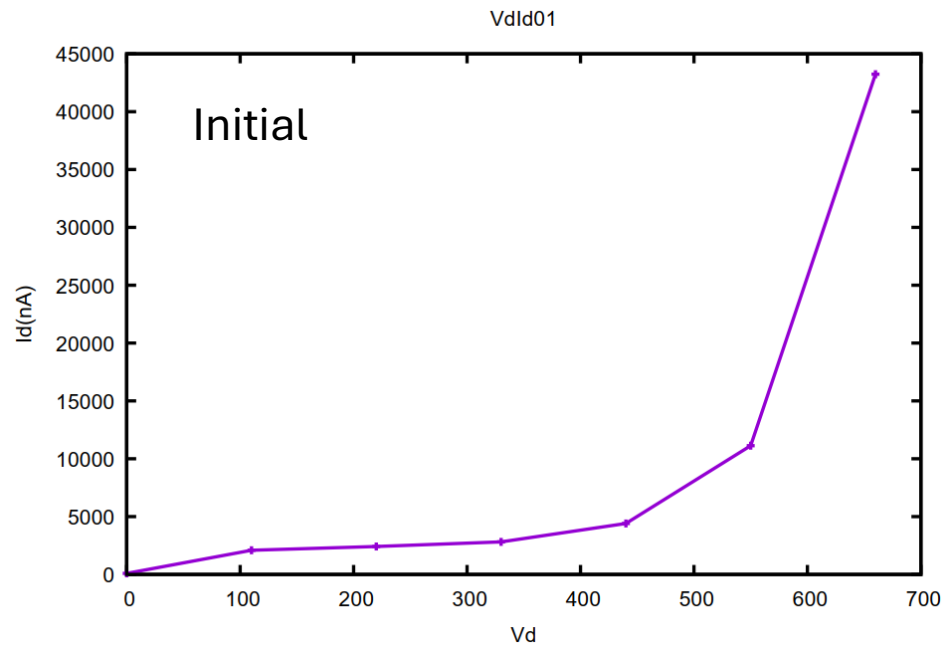
# @HT 150 °C



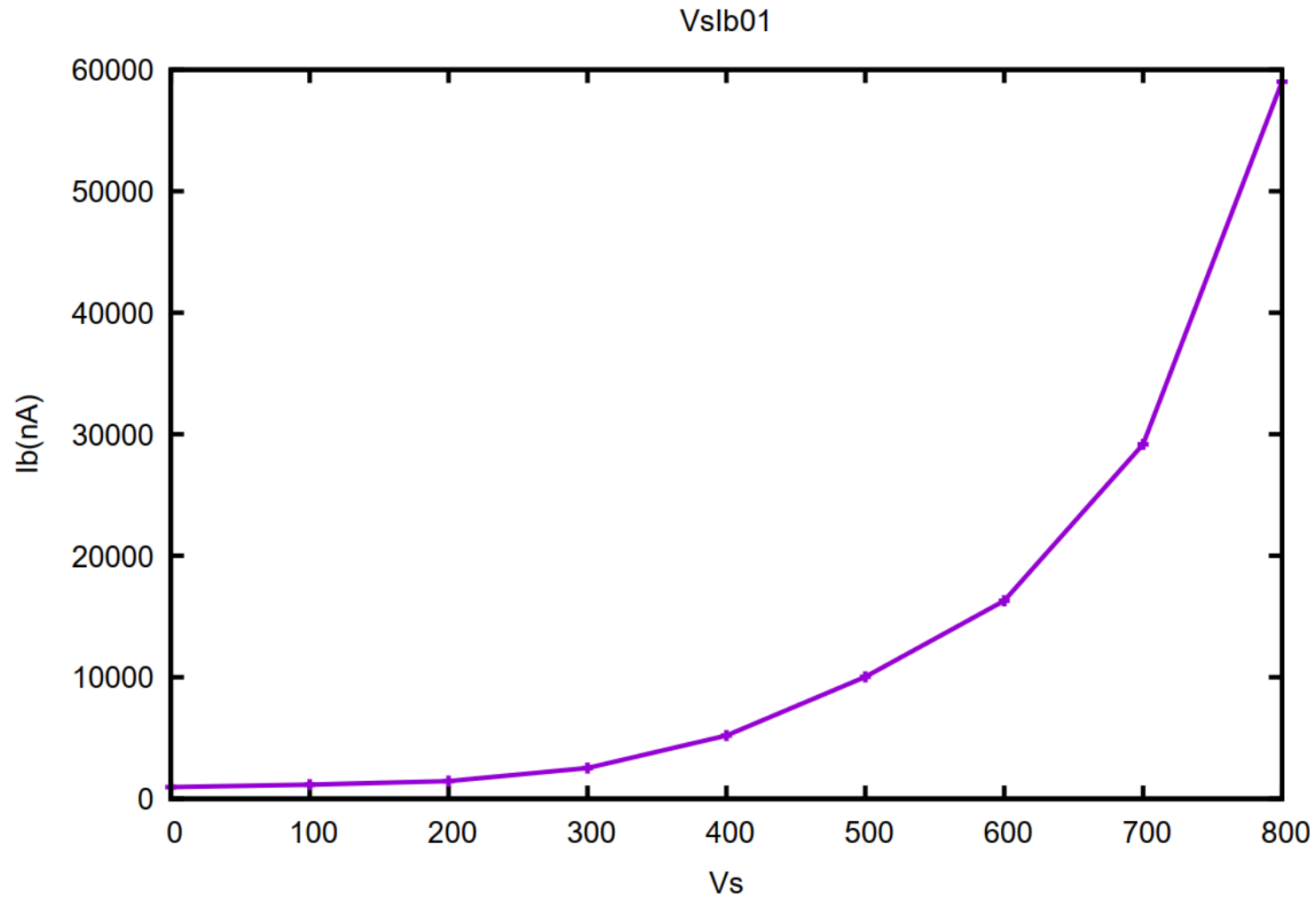
**Id-Vg transfer curve, initial @Vds=0.1V**



**Id-Vg transfer curve, after stress @Vds=0.1V**



**Drain leakage Idss versus Vd @Vg=Vs=Vb=GND**



**Bulk/substrate leakage  $I_b$  versus  $V_s$   
@ $V_g=V_s=V_d$ , B=GND**

# Content

Basic wafer info/DC data

Dynamic test data

Chip probe data

➔ App notes

# Application note on G1 (15V) driving

## Negative Gate Turn-off

As with most EMODE GaNFET, it is best to use negative turn off gate driving to achieve fast turn off. In such a case, G0 can be left not connected (NC). Negative gate voltage of -1 to -3 is recommended.

## Zero Gate Turn-off

When using G1 for driving (either 0-12V or 0-15V), it is best to wire bond a bare die of low voltage diode (max rating 20V, max current 0.5A) between G0 and G1 such that the forward direction of the diode points from G0 to G1. Caution: at light loading (less than 0.5A), turn-off may be slow.

Recommended  $R_{goff}=0$   $R_{gon}=0$  to 5 Ohm. Recommended driver: 1EDBX275F, or other driver with stronger current capability. When driving multiple Star120 dies (more than 3), it is recommended that isolated auxiliary power supply for driver should be upgraded to support  $> 0.5A$  on-state (not only instantaneous peak) current. Reference driver board design is offered to selected customers.

# Application note on G0 (6V) driving

G0 can be used as a standard EMODE p-GaN gate. Recommended  $R_{goff}=0$   $R_{gon}=5-10$  Ohm

**Choice of G1 or G0:**

**For better system reliability, G1 is recommended.**